

CC2652P SimpleLink™ Multiprotocol 2.4 GHz Wireless MCU With Integrated Power Amplifier

Device Overview

1.1 **Features**

- Microcontroller
 - Powerful 48-MHz Arm[®] Cortex[®]-M4F processor
 - EEMBC CoreMark[®] score: 148
 - 352KB of in-system Programmable Flash
 - 256KB of ROM for protocols and library functions
 - 8KB of Cache SRAM (Alternatively available as general-purpose RAM)
 - 80KB of ultra-low leakage SRAM. The SRAM is protected by parity to ensure high reliability of operation.
 - 2-Pin cJTAG and JTAG debugging
 - Supports Over-the-Air upgrade (OTA)
- Ultra-low power sensor controller with 4KB of SRAM
 - Sample, store, and process sensor data
 - Operation independent from system CPU
 - Fast wake-up for low-power operation
- TI-RTOS, drivers, Bootloader, Bluetooth® 5 Low Energy Controller, and IEEE 802.15.4 MAC in ROM for optimized application size
- RoHS-compliant package
 - 7-mm x 7-mm RGZ VQFN48 (26 GPIOs)
- Peripherals
 - Digital peripherals can be routed to any GPIO
 - 4x 32-bit or 8x 16-bit general-purpose timers
 - 12-Bit ADC, 200 kSamples/s, 8 channels
 - 2x comparators with internal reference DAC (1x continuous time, 1x ultra-low power)
 - Programmable current source
 - 2× UART
 - 2x SSI (SPI, MICROWIRE, TI)
 - $-I^2C$
 - I²S
 - Real-Time Clock (RTC)
 - AES 128- and 256-bit Crypto Accelerator
 - ECC and RSA Public Key Hardware Accelerator
 - SHA2 Accelerator (Full suite up to SHA-512)
 - True Random Number Generator (TRNG)
 - Capacitive sensing, up to 8 channels
 - Integrated temperature and battery monitor

- External system
 - On-chip Buck DC/DC converter
- Low power
 - Wide supply voltage range: 1.8 V to 3.8 V
 - Active-Mode RX: 6.9 mA
 - Active-Mode TX 0 dBm: 7.3 mA
 - Active-Mode TX 5 dBm: 9.6 mA
 - Active-Mode TX at +10 dBm: 22 mA
 - Active-Mode TX at +20 dBm: 85 mA
 - Active-Mode MCU 48 MHz (CoreMark): 3.4 mA (71 μ A/MHz)
 - Sensor Controller, Low Power-Mode, 2 MHz, running infinite loop: 30.1 μA
 - Sensor Controller, Active-Mode, 24 MHz, running infinite loop: 808 μA
 - Standby: 0.94 µA (RTC on, 80KB RAM and CPU retention)
 - Shutdown: 150 nA (wakeup on external events)
- Radio section
 - 2.4 GHz RF transceiver compatible with Bluetooth 5 Low Energy and IEEE 802.15.4 PHY and MAC
 - Excellent receiver sensitivity:
 - -100 dBm for 802.15.4 (2.4 GHz),
 - -105 dBm for Bluetooth 125-kbps (LE Coded PHY)
 - Output power up to +20 dBm with temperature compensation
 - Suitable for systems targeting compliance with worldwide radio frequency regulations
 - EN 300 328, (Europe)
 - EN 300 440 Category 2
 - FCC CFR47 Part 15
 - ARIB STD-T66 (Japan)
- Wireless protocols
 - Thread, Zigbee[®], Bluetooth[®] 5 Low Energy, IEEE 802.15.4g, IPv6-enabled smart objects (6LoWPAN), Wi-SUN[®], proprietary systems, SimpleLink™ TI 15.4-Stack (2.4 GHz), and Dynamic Multiprotocol Manager (DMM) driver.

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- Development Tools and Software
 - SimpleLink[™] CC13x2 and CC26x2 Software Development Kit (SDK)

1.2 Applications

- 2400 to 2480 MHz ISM and SRD systems (1) with down to 4 kHz of receive bandwidth
- Building automation
 - Building security systems motion detector, electronic smart lock, door and window sensor, garage door system, gateway
 - HVAC thermostat, wireless environmental sensor, HVAC system controller, gateway
 - Fire safety system smoke and heat detector, fire alarm control panel (FACP)
 - Video surveillance IP network camera
 - Elevators and escalators elevator main control panel for elevators and escalators
- See RF Core for additional details on supported protocol standards, modulation formats, and data rates.

- SmartRF™ Studio for simple radio configuration
- Sensor Controller Studio for building low-power sensing applications

Grid infrastructure

- Smart meters water meter, gas meter, electricity meter, and heat cost allocators
- Grid communications wireless communications – Long-range sensor applications
- Other alternative energy energy harvesting
- Industrial transport asset tracking
- Factory automation and control
- Medical
- Electronic point of sale (EPOS) –Electronic Shelf Label (ESL)

1.3 Description

The CC2652P device is a multiprotocol 2.4 GHz wireless microcontroller (MCU) targeting Thread, Zigbee[®], *Bluetooth*[®] 5 Low Energy, IEEE 802.15.4g, IPv6-enabled smart objects (6LoWPAN), proprietary systems, including the SimpleLink[™] TI 15.4-Stack (2.4 GHz), and concurrent multiprotocol through a Dynamic Multiprotocol Manager (DMM) driver. The device is optimized for low-power wireless communication and advanced sensing in building security systems, HVAC, and medical markets. The highlighted features of this device include:

- Wide flexibility of protocol stack support in the SimpleLink™ CC13x2 and CC26x2 Software Development Kit (SDK).
- Enable long-range and low-power applications using integrated +20 dBm high-power amplifier with best-in-class transmit current consumption at 85 mA.
- Coin-cell operation at +10 dBm with 22 mA current consumption.
- Longer battery life wireless applications with low standby current of 0.94 μA with full RAM retention.
- Industrial temperature ready with lowest standby current of 5 μA at 85 °C.
- Advanced sensing with a programmable, autonomous ultra-low power Sensor Controller CPU with fast wake-up capability. As an example, the sensor controller is capable of 1-Hz ADC sampling at 1 μ A system current.
- Low SER (Soft Error Rate) FIT (Failure-in-time) for long operation lifetime with no disruption for industrial markets with always-on SRAM parity against corruption due to potential radiation events.
- Dedicated software controlled radio controller (Arm[®] Cortex[®]-M0) providing flexible low-power RF transceiver capability to support multiple physical layers and RF standards.
- Excellent radio sensitivity and robustness (selectivity and blocking) performance for Bluetooth[®] Low Energy (-105 dBm for 125-kbps LE Coded PHY).

The CC2652P device is part of the SimpleLink™ microcontroller (MCU) platform, which consists of Wi-Fi®, *Bluetooth*® Low Energy, Thread, Zigbee®, Sub-1 GHz MCUs, and host MCUs that all share a common, easy-to-use development environment with a single core software development kit (SDK) and rich tool set. A one-time integration of the SimpleLink™ platform enables you to add any combination of the portfolio's devices into your design, allowing 100 percent code reuse when your design requirements change. For more information, visit SimpleLink™ MCU platform.



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Device Information⁽¹⁾

PART NUMBER	PACKAGE	BODY SIZE (NOM)
CC2652P1FRGZ	VQFN (48)	7.00 mm × 7.00 mm

⁽¹⁾ For the most current part, package, and ordering information for all available devices, see the Package Option Addendum in Section 9, or see the TI website.

1.4 Functional Block Diagram

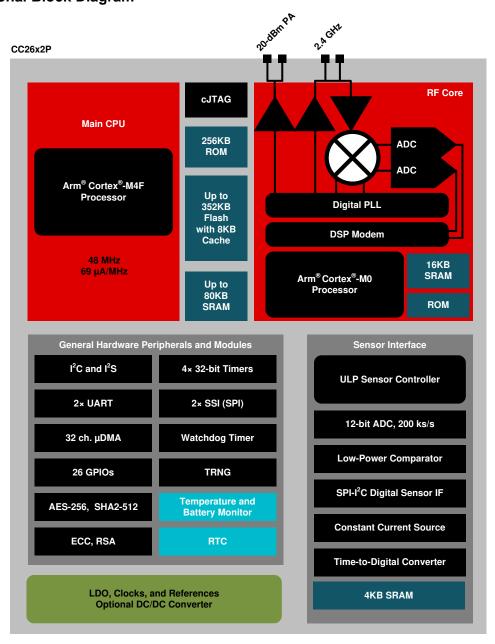


Figure 1-1. CC2652P Block Diagram



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2 Revision History

DATE	REVISION	NOTES
October 2019	*	Initial Release

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3 Device Comparison

Table 3-1. Device Family Overview

DEVICE	RADIO SUPPORT	FLASH (KB)	RAM (KB)	GPIO	PACKAGE SIZE
CC1312R	Sub-1 GHz	352	80	30	RGZ (7-mm × 7-mm VQFN48)
CC1352P	Multiprotocol Sub-1 GHz Bluetooth 5 Low Energy Zigbee Thread 2.4 GHz proprietary FSK-based formats +20-dBm high-power amplifier	352	80	26	RGZ (7-mm × 7-mm VQFN48)
CC1352R	Multiprotocol Sub-1 GHz Bluetooth 5 Low Energy Zigbee Thread 2.4 GHz proprietary FSK-based formats	352	80	28	RGZ (7-mm × 7-mm VQFN48)
CC2642R	Bluetooth 5 Low Energy 2.4 GHz proprietary FSK-based formats	352	80	31	RGZ (7-mm × 7-mm VQFN48)
CC2652R	Multiprotocol Bluetooth 5 Low Energy Zigbee Thread 2.4 GHz proprietary FSK-based formats	352	80	31	RGZ (7-mm × 7-mm VQFN48)
CC2652RB	Multiprotocol Bluetooth 5 Low Energy Zigbee Thread 2.4 GHz proprietary FSK-based formats	352	80	31	RGZ (7-mm × 7-mm VQFN48)
CC2652P	Multiprotocol Bluetooth 5 Low Energy Zigbee Thread 2.4 GHz proprietary FSK-based formats +19.5-dBm high-power amplifier	352	80	26	RGZ (7-mm × 7-mm VQFN48)
CC1310	Sub-1 GHz	32–128	16–20	10–31	RGZ (7-mm × 7-mm VQFN48) RHB (5-mm × 5-mm VQFN32) RSM (4-mm × 4-mm VQFN32)
CC1350	Sub-1 GHz Bluetooth 4.2 Low Energy	128	20	10–31	RGZ (7-mm × 7-mm VQFN48) RHB (5-mm × 5-mm VQFN32) RSM (4-mm × 4-mm VQFN32)
CC2640R2F	Bluetooth 5 Low Energy 2.4 GHz proprietary FSK-based formats	128	20	10–31	RGZ (7-mm × 7-mm VQFN48) RHB (5-mm × 5-mm VQFN32) RSM (4-mm × 4-mm VQFN32) YFV (2.7-mm × 2.7-mm DSBGA34)
CC2640R2F-Q1	Bluetooth 5 Low Energy 2.4 GHz proprietary FSK-based formats	128	20	31	RGZ (7-mm × 7-mm VQFN48)



4 Terminal Configuration and Functions

4.1 Pin Diagram – RGZ Package (Top View)

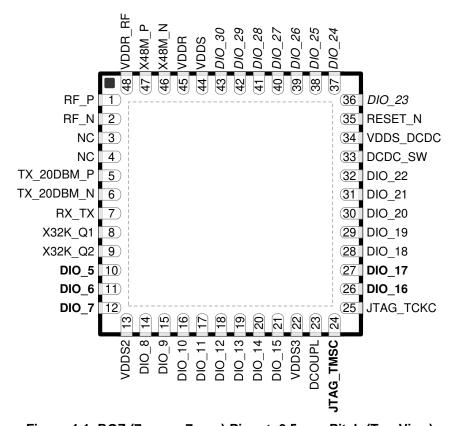


Figure 4-1. RGZ (7-mm × 7-mm) Pinout, 0.5-mm Pitch (Top View)

The following I/O pins marked in Figure 4-1 in **bold** have high-drive capabilities:

- Pin 10, DIO 5
- Pin 11, DIO_6
- Pin 12, DIO_7
- Pin 24, JTAG_TMSC
- Pin 26, DIO_16
- Pin 27, DIO_17

The following I/O pins marked in Figure 4-1 in italics have analog capabilities:

- Pin 36, DIO_23
- Pin 37, DIO 24
- Pin 38, DIO_25
- Pin 39, DIO_26
- Pin 40, DIO 27
- Pin 41, DIO_28
- Pin 42, DIO_29
- Pin 43, DIO_30

4.2 Signal Descriptions - RGZ Package

Table 4-1. Signal Descriptions - RGZ Package

PIN					
NAME	NO.	I/O TYPE		DESCRIPTION	
DCDC_SW	33	_	Power	Output from internal DC/DC converter ⁽¹⁾	
DCOUPL	23	_	Power	For decoupling of internal 1.27 V regulated digital-supply (2)	
DIO_5	10	I/O	Digital	GPIO, high-drive capability	
DIO_6	11	I/O	Digital	GPIO, high-drive capability	
DIO_7	12	I/O	Digital	GPIO, high-drive capability	
DIO_8	14	I/O	Digital	GPIO	
DIO_9	15	I/O	Digital	GPIO	
DIO_10	16	I/O	Digital	GPIO	
DIO_11	17	I/O	Digital	GPIO	
DIO_12	18	I/O	Digital	GPIO	
DIO_13	19	I/O	Digital	GPIO	
DIO_14	20	I/O	Digital	GPIO	
DIO_15	21	I/O	Digital	GPIO	
DIO_16	26	I/O	Digital	GPIO, JTAG_TDO, high-drive capability	
DIO_17	27	I/O	Digital	GPIO, JTAG_TDI, high-drive capability	
DIO_18	28	I/O	Digital	GPIO	
DIO_19	29	I/O	Digital	GPIO	
DIO_20	30	I/O	Digital	GPIO	
DIO_21	31	I/O	Digital	GPIO	
DIO_22	32	I/O	Digital	GPIO	
DIO_23	36	I/O	Digital or Analog	GPIO, analog capability	
DIO_24	37	I/O	Digital or Analog	GPIO, analog capability	
DIO_25	38	I/O	Digital or Analog	GPIO, analog capability	
DIO_26	39	I/O	Digital or Analog	GPIO, analog capability	
DIO_27	40	I/O	Digital or Analog	GPIO, analog capability	
DIO_28	41	I/O	Digital or Analog	GPIO, analog capability	
DIO_29	42	I/O	Digital or Analog	GPIO, analog capability	
DIO_30	43	I/O	Digital or Analog	GPIO, analog capability	
EGP	_	_	GND	Ground – exposed ground pad ⁽³⁾	
JTAG_TMSC	24	I/O	Digital	JTAG TMSC, high-drive capability	
JTAG_TCKC	25	I	Digital	JTAG TCKC	
RESET_N	35	ļ	Digital	Reset, active low. No internal pullup resistor	
RF_P	1	_	RF	Positive RF input signal to LNA during RX Positive RF output signal from PA during TX	
RF_N	2	_	RF	Negative RF input signal to LNA during RX Negative RF output signal from PA during TX	
RX_TX	7	_	RF	Optional bias pin for the RF LNA	
TX_20DBM_P	5	_	RF	Positive high-power TX signal	
TX_20DBM_N	6	_	RF	Negative high-power TX signal	
VDDR	45	_	Power	Internal supply, must be powered from the internal DC/DC converter or the internal LDO ⁽⁴⁾ (2)(5)	

⁽¹⁾ For more details, see technical reference manual listed in Section 8.2.

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⁽²⁾ Do not supply external circuitry from this pin.

⁽³⁾ EGP is the only ground connection for the device. Good electrical connection to device ground on printed circuit board (PCB) is imperative for proper device operation.

⁽⁴⁾ If internal DC/DC converter is not used, this pin is supplied internally from the main LDO.

⁽⁵⁾ Output from internal DC/DC and LDO is trimmed to 1.68 V.

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Table 4-1. Signal Descriptions – RGZ Package (continued)

PIN		I/O TYPE		DESCRIPTION
NAME	NO.	I/O	ITPE	DESCRIPTION
VDDR_RF	48	_	Power	Internal supply, must be powered from the internal DC/DC converter or the internal LDO $^{(6)(2)(5)}$
VDDS	44	_	Power	1.8-V to 3.8-V main chip supply ⁽¹⁾
VDDS2	13	_	Power	1.8-V to 3.8-V DIO supply ⁽¹⁾
VDDS3	22	_	Power	1.8-V to 3.8-V DIO supply ⁽¹⁾
VDDS_DCDC	34	_	Power	1.8-V to 3.8-V DC/DC converter supply
X48M_N	46	_	Analog	48-MHz crystal oscillator pin 1
X48M_P	47	_	Analog	48-MHz crystal oscillator pin 2
X32K_Q1	8	_	Analog	32-kHz crystal oscillator pin 1
X32K_Q2	9	_	Analog	32-kHz crystal oscillator pin 2

⁽⁶⁾ If internal DC/DC converter is not used, this pin must be connected to VDDR for supply from the main LDO.

4.3 Connections for Unused Pins and Modules

Table 4-2. Connections for Unused Pins

FUNCTION	SIGNAL NAME	PIN NUMBER	ACCEPTABLE PRACTICE ⁽¹⁾	PREFERRED PRACTICE ⁽¹⁾
GPIO	DIO_n	10–12 14–21 26–32 36–43	NC or GND	NC
22 769 kHz on/otal	X32K_Q1	8	NC or GND	NC
32.768-kHz crystal	X32K_Q2	9	INC OF GIND	NC
No Connects	NC	3–4	NC	NC
DC/DC converter ⁽²⁾	DCDC_SW	33	NC	NC
DC/DC convener	VDDS_DCDC	34	VDDS	VDDS

⁽¹⁾ NC = No connect

⁽²⁾ When the DC/DC converter is not used, the inductor between DCDC_SW and VDDR can be removed. VDDR and VDDR_RF must still be connected and the 22 uF DCDC capacitor must be kept on the VDDR net.

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5 Specifications

5.1 Absolute Maximum Ratings

over operating free-air temperature range (unless otherwise noted) (1) (2)

			MIN	MAX	UNIT
VDDS(3)	Supply voltage		-0.3	4.1	V
	Voltage on any digital pir	1(4)	-0.3	VDDS + 0.3, max 4.1	V
	Voltage on crystal oscilla	tor pins, X32K_Q1, X32K_Q2, X48M_N and X48M_P	-0.3	VDDR + 0.3, max 2.25	V
		Voltage scaling enabled	-0.3	VDDS	
V _{in}	Voltage on ADC input	Voltage scaling disabled, internal reference	-0.3	1.49	V
		Voltage scaling disabled, VDDS as reference	-0.3	VDDS / 2.9	
	Input level, RF pins			5	dBm
T _{stg}	Storage temperature		-40	150	°C

⁽¹⁾ Stresses beyond those listed under Absolute Maximum Ratings may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under Recommended Operating Conditions is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

5.2 ESD Ratings

				VALUE	UNIT
V	Electrostatic	Human body model (HBM), per ANSI/ESDA/JEDEC JS001 (1)	All pins	±2000	V
V _{ESD}	discharge	Charged device model (CDM), per JESD22-C101 ⁽²⁾	All pins	±500	V

⁽¹⁾ JEDEC document JEP155 states that 500-V HBM allows safe manufacturing with a standard ESD control process.

5.3 Recommended Operating Conditions

over operating free-air temperature range (unless otherwise noted)

	MIN	MAX	UNIT
Operating ambient temperature	-40	85	°C
Operating supply voltage (VDDS)	1.8	3.8	V
Rising supply voltage slew rate	0	100	mV/μs
Falling supply voltage slew rate (1)	0	20	mV/μs

⁽¹⁾ For small coin-cell batteries, with high worst-case end-of-life equivalent source resistance, a 22-μF VDDS input capacitor must be used to ensure compliance with this slew rate.

5.4 Power Supply and Modules

over operating free-air temperature range (unless otherwise noted)

1 3 1 3 1	,		
PARAMETER		TYP	UNIT
VDDS Power-on-Reset (POR) threshold		1.1 - 1.55	V
VDDS Brown-out Detector (BOD) (1)	Rising threshold	1.77	V
VDDS Brown-out Detector (BOD), before initial boot (2)	Rising threshold	1.70	V
VDDS Brown-out Detector (BOD) (1)	Falling threshold	1.75	V

⁽¹⁾ For boost mode (VDDR =1.95 V), TI drivers software initialization will trim VDDS BOD limits to maximum (approximately 2.0 V)

²⁾ All voltage values are with respect to ground, unless otherwise noted.

⁽³⁾ VDDS_DCDC, VDDS2 and VDDS3 must be at the same potential as VDDS.

⁽⁴⁾ Including analog capable DIOs.

²⁾ JEDEC document JEP157 states that 250-V CDM allows safe manufacturing with a standard ESD control process.

⁽²⁾ Brown-out Detector is trimmed at initial boot, value is kept until device is reset by a POR reset or the RESET_N pin



5.5 **Power Consumption - Power Modes**

When measured on the CC1352PEM-XD7793-XD24-PA24 reference design with T_c = 25 °C, V_{DDS} = 3.0 V with DC/DC enabled unless otherwise noted.

	PARAMETER	TEST CONDITIONS	TYP	UNIT	
Core Curre	ent Consumption				
	Reset and Shutdown	Reset. RESET_N pin asserted or VDDS below power-on-reset threshold	150	nA	
	Reset and Shutdown	Shutdown. No clocks running, no retention	150	ΠA	
I _{core}	Standby	RTC running, CPU, 80KB RAM and (partial) register retention. RCOSC_LF	0.94	μΑ	
	without cache retention	RTC running, CPU, 80KB RAM and (partial) register retention XOSC_LF	1.09	μΑ	
	Standby	RTC running, CPU, 80KB RAM and (partial) register retention. RCOSC_LF	3.2	μΑ	
	with cache retention	RTC running, CPU, 80KB RAM and (partial) register retention. XOSC_LF	3.3	μΑ	
	Idle	Supply Systems and RAM powered RCOSC_HF	675	μΑ	
	Active	MCU running CoreMark at 48 MHz RCOSC_HF	3.39	mA	
Peripheral	Current Consumption				
	Peripheral power domain	Delta current with domain enabled	97.7		
	Serial power domain	Delta current with domain enabled	7.2		
	RF Core	Delta current with power domain enabled, clock enabled, RF core idle	210.9		
	μDMA	Delta current with clock enabled, module is idle	63.9		
	Timers	Delta current with clock enabled, module is idle ⁽¹⁾	81.0		
peri	I2C	Delta current with clock enabled, module is idle	10.1	μΑ	
	128	Delta current with clock enabled, module is idle	26.3		
	SSI	Delta current with clock enabled, module is idle	82.9		
	UART	Delta current with clock enabled, module is idle (2)	167.5		
	CRYPTO (AES)	Delta current with clock enabled, module is idle ⁽³⁾	25.6		
	PKA	Delta current with clock enabled, module is idle	84.7		
	TRNG	Delta current with clock enabled, module is idle	35.6		
Sensor Co	ntroller Engine Consumption		<u>.</u>		
	Active mode	24 MHz, infinite loop	808.5		
I _{SCE}	Low-power mode	2 MHz, infinite loop	30.1	μΑ	

- Only one GPTimer running Only one UART running Only one SSI running

5.6 Power Consumption - Radio Modes

When measured on the CC1352PEM-XD7793-XD24-PA24 reference design with T_c = 25 °C, V_{DDS} = 3.0 V with DC/DC enabled unless otherwise noted.

High-power PA connected to V_{DDS} unless otherwise noted.

PARAMETER	TEST CONDITIONS	TYP	UNIT
Radio receive current	2440 MHz	6.9	mA
Radio transmit current	0 dBm output power setting 2440 MHz	7.3	mA
Regular PA	+5 dBm output power setting 2440 MHz	9.6	mA
Radio transmit current High-power PA	+20 dBm output power setting 2440 MHz	85	mA
Radio transmit current High-power PA, 10 dBm configuration ⁽¹⁾	+10 dBm output power setting 2440 MHz	22	mA

⁽¹⁾ Measured on evaluation board as described in https://www.ti.com/lit/pdf/swra636.

5.7 Nonvolatile (Flash) Memory Characteristics

Over operating free-air temperature range and V_{DDS} = 3.0 V (unless otherwise noted)

PARAMETER	TEST CONDITIONS	MIN	TYP	MAX	UNIT
Flash sector size			8		KB
Supported flash erase cycles before failure, full bank ⁽¹⁾		30			k Cycles
Supported flash erase cycles before failure, single sector ⁽²⁾		60			k Cycles
Maximum number of write operations per row before sector erase ⁽³⁾				83	Write Operations
Flash retention	105 °C	11.4			Years at 105 °C
Flash sector erase current	Average delta current		10.7		mA
Flash sector erase time ⁽⁴⁾			10		ms
Flash write current	Average delta current, 4 bytes at a time		6.2		mA
Flash write time ⁽⁴⁾	4 bytes at a time		21.6		μs

⁽¹⁾ A full bank erase is counted as a single erase cycle on each sector

STRUMENTS

⁽²⁾ Up to 4 customer-designated sectors can be individually erased an additional 30k times beyond the baseline bank limitation of 30k cycles

⁽³⁾ Each wordline is 2048 bits (or 256 bytes) wide. This limitation corresponds to sequential memory writes of 4 (3.1) bytes minimum per write over a whole wordline. If additional writes to the same wordline are required, a sector erase is required once the maximum number of write operations per row is reached.

⁽⁴⁾ This number is dependent on Flash aging and increases over time and erase cycles



5.8 Thermal Resistance Characteristics

		PACKAGE	
THERMAL METRIC ⁽¹⁾		RGZ (VQFN)	UNIT
		48 PINS	
$R_{\theta JA}$	Junction-to-ambient thermal resistance	23.4	°C/W ⁽²⁾
R ₀ JC(top)	Junction-to-case (top) thermal resistance	13.3	°C/W ⁽²⁾
$R_{\theta JB}$	Junction-to-board thermal resistance	8.0	°C/W ⁽²⁾
ΨЈТ	Junction-to-top characterization parameter	0.1	°C/W ⁽²⁾
ΨЈВ	Junction-to-board characterization parameter	7.9	°C/W ⁽²⁾
R ₀ JC(bot)	Junction-to-case (bottom) thermal resistance	1.7	°C/W ⁽²⁾

⁽¹⁾ For more information about traditional and new thermal metrics, see Semiconductor and IC Package Thermal Metrics.

^{(2) °}C/W = degrees Celsius per watt.

NSTRUMENTS

Bluetooth Low Energy - Receive (RX)

Measured on the CC1352PEM-XD7793-XD24-PA24 reference design with T_c = 25 °C, V_{DDS} = 3.0 V, f_{RF} = 2440 MHz with DC/DC enabled and high power PA connected to $\ensuremath{V_{\text{DDS}}}$ unless otherwise noted.

All measurements are performed at the antenna input with a combined RX and TX path, except for high power PA which is measured at a dedicated antenna connection.

All measurements are performed conducted.

PARAMETER	TEST CONDITIONS	MIN TYP	MAX	UNIT
125 kbps (LE Coded)				
Receiver sensitivity	Differential mode. BER = 10^{-3}	-105		dBm
Receiver saturation	Differential mode. BER = 10^{-3}	>5		dBm
Frequency error tolerance	Difference between the incoming carrier frequency and the internally generated carrier frequency	> (-300 / 300)		kHz
Data rate error tolerance	Difference between incoming data rate and the internally generated data rate (37-byte packets)	> (-320 / 240)		ppm
Data rate error tolerance	Difference between incoming data rate and the internally generated data rate (255-byte packets)	> (-125 / 125)		ppm
Co-channel rejection ⁽¹⁾	Wanted signal at -79 dBm, modulated interferer in channel, BER = 10^{-3}	-1.5		dB
Selectivity, ±1 MHz ⁽¹⁾	Wanted signal at –79 dBm, modulated interferer at ±1 MHz, BER = 10 ⁻³	8 / 4.5 ⁽²⁾		dB
Selectivity, ±2 MHz ⁽¹⁾	Wanted signal at –79 dBm, modulated interferer at ±2 MHz, BER = 10 ⁻³	44 / 39 ⁽²⁾		dB
Selectivity, ±3 MHz ⁽¹⁾	Wanted signal at –79 dBm, modulated interferer at ±3 MHz, BER = 10 ⁻³	46 / 44 ⁽²⁾		dB
Selectivity, ±4 MHz ⁽¹⁾	Wanted signal at –79 dBm, modulated interferer at ±4 MHz, BER = 10 ⁻³	44 / 46 ⁽²⁾		dB
Selectivity, ±6 MHz ⁽¹⁾	Wanted signal at –79 dBm, modulated interferer at $\ge \pm 6$ MHz, BER = 10^{-3}	48 / 44 ⁽²⁾		dB
Selectivity, ±7 MHz	Wanted signal at -79 dBm, modulated interferer at $\ge \pm 7$ MHz, BER = 10^{-3}	51 / 45 ⁽²⁾		dB
Selectivity, Image frequency ⁽¹⁾	Wanted signal at –79 dBm, modulated interferer at image frequency, BER = 10 ⁻³	39		dB
Selectivity, Image frequency ±1 MHz ⁽¹⁾	Note that Image frequency + 1 MHz is the Co- channel –1 MHz. Wanted signal at –79 dBm, modulated interferer at ±1 MHz from image frequency, BER = 10 ⁻³	4.5 / 44 (2)		dB
500 kbps (LE Coded)				
Receiver sensitivity	Differential mode. BER = 10^{-3}	-100		dBm
Receiver saturation	Differential mode. BER = 10 ⁻³	> 5		dBm
Frequency error tolerance	Difference between the incoming carrier frequency and the internally generated carrier frequency	> (-300 / 300)		kHz
Data rate error tolerance	Difference between incoming data rate and the internally generated data rate (37-byte packets)	> (-450 / 450)		ppm
Data rate error tolerance	Difference between incoming data rate and the internally generated data rate (255-byte packets)	> (-175 / 175)		ppm
Co-channel rejection (1)	Wanted signal at -72 dBm, modulated interferer in channel, BER = 10^{-3}	-3.5		dB
Selectivity, ±1 MHz ⁽¹⁾	Wanted signal at –72 dBm, modulated interferer at ±1 MHz, BER = 10 ⁻³	8 / 4 ⁽²⁾		dB
Selectivity, ±2 MHz ⁽¹⁾	Wanted signal at –72 dBm, modulated interferer at ±2 MHz, BER = 10 ⁻³	44 / 37 (2)		dB
Selectivity, ±3 MHz ⁽¹⁾	Wanted signal at –72 dBm, modulated interferer at ±3 MHz, BER = 10 ⁻³	46 / 46 (2)		dB
Selectivity, ±4 MHz ⁽¹⁾	Wanted signal at –72 dBm, modulated interferer at ±4 MHz, BER = 10 ⁻³	45 / 47 (2)		dB
Selectivity, ±6 MHz ⁽¹⁾	Wanted signal at -72 dBm, modulated interferer at $\ge \pm 6$ MHz, BER = 10^{-3}	46 / 45 (2)		dB
Selectivity, ±7 MHz	Wanted signal at -72 dBm, modulated interferer at $\ge \pm 7$ MHz, BER = 10^{-3}	49 / 45 ⁽²⁾		dB
	•			

Numbers given as I/C dB

X / Y, where X is +N MHz and Y is -N MHz (2)



Bluetooth Low Energy - Receive (RX) (continued)

Measured on the CC1352PEM-XD7793-XD24-PA24 reference design with T_c = 25 °C, V_{DDS} = 3.0 V, f_{RF} = 2440 MHz with DC/DC enabled and high power PA connected to V_{DDS} unless otherwise noted.

All measurements are performed at the antenna input with a combined RX and TX path, except for high power PA which is measured at a dedicated antenna connection.

All measurements are perfo PARAMETER	TEST CONDITIONS	MIN TYP	MAX	UNIT
Selectivity, Image frequency ⁽¹⁾	Wanted signal at –72 dBm, modulated interferer at image frequency, BER = 10 ⁻³	37		dB
Selectivity, Image frequency ±1 MHz ⁽¹⁾	Note that Image frequency + 1 MHz is the Co- channel –1 MHz. Wanted signal at –72 dBm, modulated interferer at ±1 MHz from image frequency, BER = 10 ⁻³	4 / 46(2)		dB
1 Mbps (LE 1M)				
Receiver sensitivity	Differential mode. BER = 10^{-3}	-97		dBm
Receiver saturation	Differential mode. BER = 10 ⁻³	> 5		dBm
Frequency error tolerance	Difference between the incoming carrier frequency and the internally generated carrier frequency	> (-350 / 350)		kHz
Data rate error tolerance	Difference between incoming data rate and the internally generated data rate (37-byte packets)	> (-750 / 750)		ppm
Co-channel rejection ⁽¹⁾	Wanted signal at -67 dBm , modulated interferer in channel, BER = 10^{-3}	-6		dB
Selectivity, ±1 MHz ⁽¹⁾	Wanted signal at -67 dBm, modulated interferer at ± 1 MHz, BER = 10^{-3}	7 / 4 ⁽²⁾		dB
Selectivity, ±2 MHz ⁽¹⁾	Wanted signal at –67 dBm, modulated interferer at ±2 MHz,BER = 10 ⁻³	40 / 33 (2)		dB
Selectivity, ±3 MHz ⁽¹⁾	Wanted signal at –67 dBm, modulated interferer at ±3 MHz, BER = 10^{-3}	36 / 41 ⁽²⁾		dB
Selectivity, ±4 MHz ⁽¹⁾	Wanted signal at –67 dBm, modulated interferer at ±4 MHz, BER = 10 ⁻³	36 / 45 ⁽²⁾		dB
Selectivity, ±5 MHz or more ⁽¹⁾	Wanted signal at –67 dBm, modulated interferer at \geq ±5 MHz, BER = 10^{-3}	40		dB
Selectivity, image frequency ⁽¹⁾	Wanted signal at –67 dBm, modulated interferer at image frequency, BER = 10 ⁻³	33		dB
Selectivity, image frequency ±1 MHz ⁽¹⁾	Note that Image frequency + 1 MHz is the Co- channel –1 MHz. Wanted signal at –67 dBm, modulated interferer at ±1 MHz from image frequency, BER = 10 ⁻³	4 / 41 (2)		dB
Out-of-band blocking (3)	30 MHz to 2000 MHz	-10		dBm
Out-of-band blocking	2003 MHz to 2399 MHz	-18		dBm
Out-of-band blocking	2484 MHz to 2997 MHz	-12		dBm
Out-of-band blocking	3000 MHz to 12.75 GHz	-2		dBm
Intermodulation	Wanted signal at 2402 MHz, –64 dBm. Two interferers at 2405 and 2408 MHz respectively, at the given power level	-42		dBm
Spurious emissions, 30 to 1000 MHz ⁽⁴⁾	Measurement in a 50- Ω single-ended load.	< -59		dBm
Spurious emissions, 1 to 12.75 GHz ⁽⁴⁾	Measurement in a 50 Ω single-ended load.	< -47		dBm
RSSI dynamic range		70		dB
RSSI accuracy		±4		dB
2 Mbps (LE 2M)			т	
Receiver sensitivity	Differential mode. Measured at SMA connector, BER = 10^{-3}	-92		dBm
Receiver saturation	Differential mode. Measured at SMA connector, BER = 10^{-3}	> 5		dBm
Frequency error tolerance	Difference between the incoming carrier frequency and the internally generated carrier frequency	> (-500 / 500)		kHz

⁽³⁾ Excluding one exception at F_{wanted} / 2, per Bluetooth Specification

⁽⁴⁾ Suitable for systems targeting compliance with worldwide radio-frequency regulations ETSI EN 300 328 and EN 300 440 Class 2 (Europe), FCC CFR47 Part 15 (US), and ARIB STD-T66 (Japan)



Bluetooth Low Energy - Receive (RX) (continued)

Measured on the CC1352PEM-XD7793-XD24-PA24 reference design with T_c = 25 °C, V_{DDS} = 3.0 V, f_{RF} = 2440 MHz with DC/DC enabled and high power PA connected to $V_{\mbox{\scriptsize DDS}}$ unless otherwise noted.

All measurements are performed at the antenna input with a combined RX and TX path, except for high power PA which is measured at a dedicated antenna connection.

All measurements are performed conducted

PARAMETER	TEST CONDITIONS	MIN	TYP	MAX	UNIT
Data rate error tolerance	Difference between incoming data rate and the internally generated data rate (37-byte packets)		> (-700 / 750)		ppm
Co-channel rejection ⁽¹⁾	Wanted signal at -67 dBm, modulated interferer in channel,BER = 10^{-3}		-7		dB
Selectivity, ±2 MHz ⁽¹⁾	Wanted signal at –67 dBm, modulated interferer at ±2 MHz, Image frequency is at –2 MHz, BER = 10^{-3}		8 / 4 ⁽²⁾		dB
Selectivity, ±4 MHz ⁽¹⁾	Wanted signal at –67 dBm, modulated interferer at ± 4 MHz, BER = 10^{-3}		36 / 36 ⁽²⁾		dB
Selectivity, ±6 MHz ⁽¹⁾	Wanted signal at –67 dBm, modulated interferer at ± 6 MHz, BER = 10^{-3}		37 / 36 ⁽²⁾		dB
Selectivity, image frequency ⁽¹⁾	Wanted signal at -67 dBm, modulated interferer at image frequency, BER = 10^{-3}		4		dB
Selectivity, image frequency ±2 MHz ⁽¹⁾	Note that Image frequency + 2 MHz is the Co-channel. Wanted signal at –67 dBm, modulated interferer at ±2 MHz from image frequency, BER = 10 ⁻³		-7 / 36 ⁽²⁾		dB
Out-of-band blocking (3)	30 MHz to 2000 MHz		-16		dBm
Out-of-band blocking	2003 MHz to 2399 MHz		-21		dBm
Out-of-band blocking	2484 MHz to 2997 MHz		-15		dBm
Out-of-band blocking	3000 MHz to 12.75 GHz		-12		dBm
Intermodulation	Wanted signal at 2402 MHz, –64 dBm. Two interferers at 2405 and 2408 MHz respectively, at the given power level		-38		dBm

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5.10 Bluetooth Low Energy - Transmit (TX)

Measured on the CC1352PEM-XD7793-XD24-PA24 reference design with T_c = 25 °C, V_{DDS} = 3.0 V, f_{RF} = 2440 MHz with DC/DC enabled and high power PA connected to V_{DDS} unless otherwise noted.

All measurements are performed at the antenna input with a combined RX and TX path, except for high power PA which is measured at a dedicated antenna connection.

All measurements are performed conducted.

PARAMETER		TEST CONDITIONS	MIN TYP	MAX	UNIT
General Parameters					
Max output power, high power PA	Differential mode, delivered to a sing	gle-ended 50 Ω load through a balun	19.5		dBm
Output power programmable range high power PA	Differential mode, delivered to a sing	ferential mode, delivered to a single-ended 50 Ω load through a balun			dB
Max output power, high power PA, 10 dBm configuration ⁽¹⁾	Differential mode, delivered to a sing	gle-ended 50 Ω load through a balun	10.5		dBm
Output power programmable range high power PA, 10 dBm configuration ⁽¹⁾	Differential mode, delivered to a sing	gle-ended 50 Ω load through a balun	5		dB
Max output power, regular PA	Differential mode, delivered to a sing	Differential mode, delivered to a single-ended 50 Ω load through a balun			dBm
Output power programmable range, regular PA	Differential mode, delivered to a sing	26		dB	
Spurious emissions a	nd harmonics				
	f < 1 GHz, outside restricted bands	+20 dBm setting	< -36		dBm
Spurious emissions, high-power PA ⁽²⁾⁽³⁾	f < 1 GHz, restricted bands FCC		< -55		dBm
g power . 7.	f > 1 GHz, including harmonics		-37		dBm
Harmonics,	Second harmonic		-35		dBm
high-power PA ⁽²⁾⁽⁴⁾	Third harmonic		-42		dBm
Caurious amissisms	f < 1 GHz, outside restricted bands		< -36		dBm
Spurious emissions, high-power PA, 10	f < 1 GHz, restricted bands ETSI		< -54		dBm
dBm configuration ⁽²⁾⁽³⁾⁽¹⁾	f < 1 GHz, restricted bands FCC		< -55		dBm
Comiguration	f > 1 GHz, including harmonics	+10 dBm setting ⁽¹⁾	-41		dBm
Harmonics,	Second harmonic		< -42		dBm
high-power PA, 10 dBm configuration ⁽²⁾⁽¹⁾	Third harmonic		< -42		dBm
	f < 1 GHz, outside restricted bands		< -36		dBm
Spurious emissions,	f < 1 GHz, restricted bands ETSI		< -54		dBm
regular PA ⁽²⁾	f < 1 GHz, restricted bands FCC	LE dPm cotting	< -55		dBm
	f > 1 GHz, including harmonics	+5 dBm setting	< -42		dBm
Harmonics,	Second harmonic		< -42		dBm
regular PA ⁽²⁾	Third harmonic		< -42		dBm

- (1) Measured on evaluation board as described in www.ti.com/lit/pdf/swra636.
- (2) Suitable for systems targeting compliance with worldwide radio-frequency regulations ETSI EN 300 328 and EN 300 440 Class 2 (Europe), FCC CFR47 Part 15 (US), and ARIB STD-T66 (Japan).
- (3) To ensure margins for passing FCC band edge requirements at 2483.5 MHz, a lower than maximum output-power setting or less than 100% duty cycle may be used when operating at the upper BLE channel(s).
- (4) To ensure margins for passing FCC requirements for harmonic emission, duty cycling may be required. The CC1352P-2 LaunchPad reference design should also be reviewed as the filter provides higher attenuation of harmonics compared to the CC1352PEM-XD7793-XD24-PA24 reference design.



5.11 Zigbee and Thread - IEEE 802.15.4-2006 2.4 GHz (OQPSK DSSS1:8, 250 kbps) - RX

Measured on the CC1352PEM-XD7793-XD24-PA24 reference design with T_c = 25 °C, V_{DDS} = 3.0 V, f_{RF} = 2440 MHz with DC/DC enabled and high power PA connected to V_{DDS} unless otherwise noted.

All measurements are performed at the antenna input with a combined RX and TX path, except for high power PA which is measured at a dedicated antenna connection.

All measurements are performed conducted.

PARAMETER	TEST CONDITIONS	MIN TYP MAX	UNIT
Receiver sensitivity	PER = 1%	-100	dBm
Receiver saturation	PER = 1%	> 5	dBm
Adjacent channel rejection	Wanted signal at –82 dBm, modulated interferer at ±5 MHz, PER = 1%	36	dB
Alternate channel rejection	Wanted signal at –82 dBm, modulated interferer at ±10 MHz, PER = 1%	57	dB
Channel rejection, ±15 MHz or more	Wanted signal at –82 dBm, undesired signal is IEEE 802.15.4 modulated channel, stepped through all channels 2405 to 2480 MHz, PER = 1%	59	dB
Blocking and desensitization, 5 MHz from upper band edge	Wanted signal at –97 dBm (3 dB above the sensitivity level), CW jammer, PER = 1%	57	dB
Blocking and desensitization, 10 MHz from upper band edge	Wanted signal at –97 dBm (3 dB above the sensitivity level), CW jammer, PER = 1%	63	dB
Blocking and desensitization, 20 MHz from upper band edge	Wanted signal at –97 dBm (3 dB above the sensitivity level), CW jammer, PER = 1%	63	dB
Blocking and desensitization, 50 MHz from upper band edge	Wanted signal at –97 dBm (3 dB above the sensitivity level), CW jammer, PER = 1%	66	dB
Blocking and desensitization, –5 MHz from lower band edge	Wanted signal at –97 dBm (3 dB above the sensitivity level), CW jammer, PER = 1%	60	dB
Blocking and desensitization, –10 MHz from lower band edge	Wanted signal at –97 dBm (3 dB above the sensitivity level), CW jammer, PER = 1%	60	dB
Blocking and desensitization, –20 MHz from lower band edge	Wanted signal at –97 dBm (3 dB above the sensitivity level), CW jammer, PER = 1%	63	dB
Blocking and desensitization, –50 MHz from lower band edge	Wanted signal at –97 dBm (3 dB above the sensitivity level), CW jammer, PER = 1%	65	dB
Spurious emissions, 30 MHz to 1000 MHz	Measurement in a 50-Ω single-ended load	-66	dBm
Spurious emissions, 1 GHz to 12.75 GHz	Measurement in a 50-Ω single-ended load	-53	dBm
Frequency error tolerance	Difference between the incoming carrier frequency and the internally generated carrier frequency	> 350	ppm
Symbol rate error tolerance	Difference between incoming symbol rate and the internally generated symbol rate	> 1000	ppm
RSSI dynamic range		95	dB
RSSI accuracy		±4	dB



5.12 Zigbee and Thread - IEEE 802.15.4-2006 2.4 GHz (OQPSK DSSS1:8, 250 kbps) - TX

Measured on the CC1352PEM-XD7793-XD24-PA24 reference design with T_c = 25 °C, V_{DDS} = 3.0 V, f_{RF} = 2440 MHz with DC/DC enabled and high power PA connected to V_{DDS} unless otherwise noted.

All measurements are performed at the antenna input with a combined RX and TX path, except for high power PA which is measured at a dedicated antenna connection.

All measurements are performed conducted

PARAMETER		TEST CONDITIONS	MIN TYP	MAX	UNIT
General Parameters					
Max output power, high power PA	Differential mode, delivered to a si	ngle-ended 50-Ω load through a balun	19.5		dBm
Output power programmable range, high power PA	Differential mode, delivered to a si	ifferential mode, delivered to a single-ended 50- Ω load through a balun			dB
Max output power, high power PA, 10 dBm configuration ⁽¹⁾	Differential mode, delivered to a si	ngle-ended 50- Ω load through a balun	10.5		dBm
Output power programmable range, high power PA, 10 dBm configuration ⁽¹⁾	Differential mode, delivered to a si	ngle-ended 50- Ω load through a balun	5		dB
Max output power, regular PA	Differential mode, delivered to a si	ngle-ended 50- Ω load through a balun	5		dBm
Output power programmable range, regular PA	Differential mode, delivered to a si	Differential mode, delivered to a single-ended 50- Ω load through a balun			dB
Spurious emissions and	harmonics			*	
Spurious emissions, high-power PA ⁽²⁾⁽³⁾	f < 1 GHz, outside restricted bands	+20 dBm setting	< -39		dBm
	f < 1 GHz, restricted bands FCC		< -49		dBm
	f > 1 GHz, including harmonics		-40		dBm
Harmonics,	Second harmonic		-35		dBm
high-power PA ⁽²⁾⁽⁴⁾	Third harmonic		-42		dBm
	f < 1 GHz, outside restricted bands	+10 dBm setting ⁽¹⁾	< -36		dBm
Spurious emissions, high-power PA, 10 dBm	f < 1 GHz, restricted bands ETSI		< -47		dBm
configuration (2)(3)(1)	f < 1 GHz, restricted bands FCC		< -55		dBm
	f > 1 GHz, including harmonics	TTO UDITI Setting	-42		dBm
Harmonics,	Second harmonic		< -42		dBm
high-power PA, 10 dBm configuration (2)(1)	Third harmonic		< -42		dBm
J. J.	f < 1 GHz, outside restricted bands		< -36		dBm
Spurious emissions,	f < 1 GHz, restricted bands ETSI		< -47		dBm
regular PA ⁽²⁾⁽⁵⁾	f < 1 GHz, restricted bands FCC	+5 dBm setting	< -55		dBm
	f > 1 GHz, including harmonics	To ability	< -42		dBm
Harmonics,	Second harmonic		< -42		dBm
regular PA ⁽²⁾ Third harmonic			< -42		dBm
IEEE 802.15.4-2006 2.4 G	GHz (OQPSK DSSS1:8, 250 kbps)				
Error vector magnitude, high power PA	+20 dBm setting		2		%
Error vector magnitude, high power PA, 10 dBm configuration ⁽¹⁾	+10 dBm setting		2		%

- (1) Measured on evaluation board as described in https://www.ti.com/lit/pdf/swra636.
- (2) Suitable for systems targeting compliance with worldwide radio-frequency regulations ETSI EN 300 328 and EN 300 440 Class 2 (Europe), FCC CFR47 Part 15 (US), and ARIB STD-T66 (Japan).
- (3) To ensure margins for passing FCC band edge requirements at 2483.5 MHz, a lower than maximum output-power setting or less than 100% duty cycle may be used when operating at the upper 802.15.4 channel(s).
- (4) To ensure margins for passing FCC requirements for harmonic emission, duty cycling may be required. The CC1352P-2 LaunchPad reference design should also be reviewed as the filter provides higher attenuation of harmonics compared to the CC1352PEM-XD7793-XD24-PA24 reference design.
- (5) To ensure margins for passing FCC band edge requirements at 2483.5 MHz, a lower than maximum output-power setting or less than 100% duty cycle may be used when operating at 2480 MHz.



Zigbee and Thread - IEEE 802.15.4-2006 2.4 GHz (OQPSK DSSS1:8, 250 kbps) - TX (continued)

Measured on the CC1352PEM-XD7793-XD24-PA24 reference design with T_c = 25 °C, V_{DDS} = 3.0 V, f_{RF} = 2440 MHz with DC/DC enabled and high power PA connected to $V_{\mbox{\scriptsize DDS}}$ unless otherwise noted.

All measurements are performed at the antenna input with a combined RX and TX path, except for high power PA which is measured at a dedicated antenna connection.

All measurements are performed conducted.

PARAMETER	TEST CONDITIONS	MIN	TYP	MAX	UNIT
Error vector magnitude Regular PA	+5 dBm setting		2		%

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5.13 Timing and Switching Characteristics

Table 5-1. Reset Timing

PARAMETER	MIN	TYP MAX	UNIT
RESET_N low duration	1		μs

Table 5-2. Wakeup Timing

Measured over operating free-air temperature with $V_{DDS} = 3.0 \text{ V}$ (unless otherwise noted). The times listed here do not include software overhead.

PARAMETER	TEST CONDITIONS	MIN	TYP	MAX	UNIT
MCU, Reset to Active ⁽¹⁾		8	50 - 3000		μs
MCU, Shutdown to Active ⁽¹⁾		8	50 - 3000		μs
MCU, Standby to Active			160		μs
MCU, Active to Standby			36		μs
MCU, Idle to Active			14		μs

⁽¹⁾ The wakeup time is dependent on remaining charge on VDDR capacitor when starting the device, and thus how long the device has been in Reset or Shutdown before starting up again.



5.13.1 Clock Specifications

Table 5-3. 48 MHz Crystal Oscillator (XOSC HF)

Measured on a Texas Instruments reference design with $T_c = 25$ °C, $V_{DDS} = 3.0$ V, unless otherwise noted. (1)

	PARAMETER	MIN	TYP	MAX	UNIT
	Crystal frequency		48		MHz
ESR	Equivalent series resistance $6 \text{ pF} < C_L \le 9 \text{ pF}$		20	60	Ω
ESR	Equivalent series resistance 5 pF $<$ C _L \le 6 pF			80	Ω
L _M	Motional inductance, relates to the load capacitance that is used for the crystal (C _L in Farads) ⁽²⁾		$< 3 \times 10^{-24} / C_L^2$		Н
C _L	Crystal load capacitance (3)	5	7 ⁽⁴⁾	9	pF
	Start-up time ⁽⁵⁾		200		μs

- (1) Probing or otherwise stopping the crystal while the DC/DC converter is enabled may cause permanent damage to the device.
- (2) The crystal manufacturer's specification must satisfy this requirement for proper operation.
- (3) Adjustable load capacitance is integrated into the device. External load capacitors are required for systems targeting compliance with certain regulations. See the device errata for further details.
- (4) On-chip default connected capacitance including reference design parasitic capacitance. Connected internal capacitance is changed through software in the Customer Configuration section (CCFG).
- (5) Start-up time using the TI-provided power driver. Start-up time may increase if driver is not used.

Table 5-4. 48 MHz RC Oscillator (RCOSC_HF)

Measured on a Texas Instruments reference design with T_c = 25 °C, V_{DDS} = 3.0 V, unless otherwise noted.

	MIN	TYP	MAX	UNIT
Frequency		48		MHz
Uncalibrated frequency accuracy		±1		%
Calibrated frequency accuracy ⁽¹⁾		±0.25		%
Start-up time		5		μs

(1) Accuracy relative to the calibration source (XOSC_HF)

Table 5-5. 2 MHz RC Oscillator (RCOSC_MF)

Measured on a Texas Instruments reference design with $T_c = 25$ °C, $V_{DDS} = 3.0$ V, unless otherwise noted.

<u></u>	ססס				
		MIN	TYP	MAX	UNIT
Calibrated frequency			2		MHz
Start-up time			5		μs

Table 5-6. 32.768 kHz Crystal Oscillator (XOSC LF)

Measured on a Texas Instruments reference design with T_c = 25 °C, V_{DDS} = 3.0 V, unless otherwise noted.

		MIN	TYP	MAX	UNIT
	Crystal frequency		32.768		kHz
ESR	Equivalent series resistance		30	100	kΩ
C_{L}	Crystal load capacitance	6	7 ⁽¹⁾	12	pF

Default load capacitance using TI reference designs including parasitic capacitance. Crystals with different load capacitance may be used

Table 5-7. 32 kHz RC Oscillator (RCOSC_LF)

Measured on a Texas Instruments reference design with T_c = 25 °C, V_{DDS} = 3.0 V, unless otherwise noted.

0 0 1 220	·			
	MIN	TYP	MAX	UNIT
Calibrated frequency		32.8 ⁽¹⁾		kHz
Temperature coefficient		50		ppm/°C

⁽¹⁾ When using RCOSC_LF as source for the low frequency system clock (SCLK_LF), the accuracy of the SCLK_LF-derived Real Time Clock (RTC) can be improved by measuring RCOSC_LF relative to XOSC_HF and compensating for the RTC tick speed. This functionality is available through the TI-provided Power driver.

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5.13.2 Synchronous Serial Interface (SSI) Characteristics

Table 5-8. Synchronous Serial Interface (SSI) Characteristics

over operating free-air temperature range (unless otherwise noted)

PARAMETER NO.		PARAMETER	MIN	TYP	MAX	UNIT
S1	t _{clk_per}	SSICIk cycle time	12		65024	System Clocks (1)
S2 ⁽²⁾	t _{clk_high}	SSICIk high time		0.5		t _{clk_per}
S3 ⁽²⁾	t _{clk_low}	SSICIk low time		0.5		t _{clk_per}

- (1) When using the TI-provided Power driver, the SSI system clock is always 48 MHz.
- (2) Refer to SSI timing diagrams Figure 5-1, Figure 5-2, and Figure 5-3.

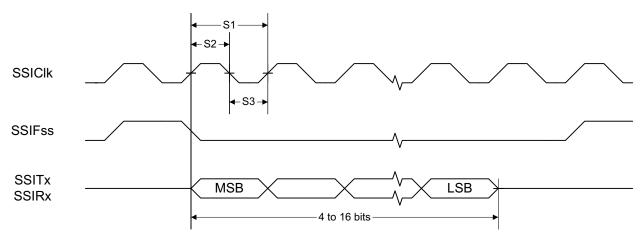


Figure 5-1. SSI Timing for TI Frame Format (FRF = 01), Single Transfer Timing Measurement

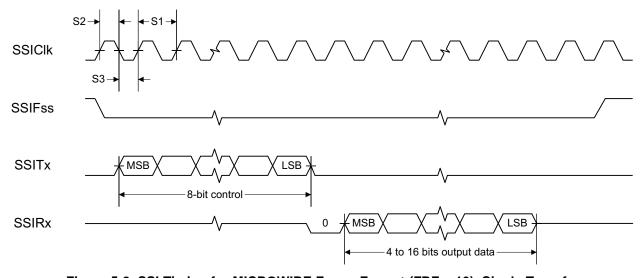


Figure 5-2. SSI Timing for MICROWIRE Frame Format (FRF = 10), Single Transfer

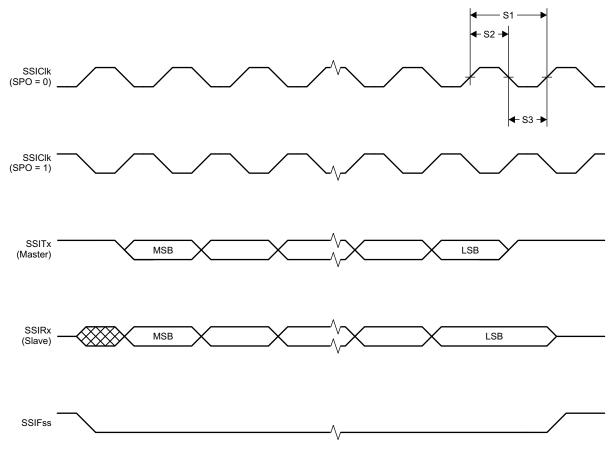


Figure 5-3. SSI Timing for SPI Frame Format (FRF = 00), With SPH = 1

5.13.3 UART

Table 5-9. Continuous Time Comparator

 $T_c = 25$ °C, $V_{DDS} = 3.0$ V, unless otherwise noted.

PARAMETER	TEST CONDITIONS	MIN	TYP	MAX	UNIT
Input voltage range ⁽¹⁾		0		V_{DDS}	V
Offset	Measured at V _{DDS} / 2		±5		mV
Decision time	Step from -10 mV to 10 mV		0.78		μs
Current consumption	Internal reference		8.6		μΑ

The input voltages can be generated externally and connected throughout I/Os or an internal reference voltage can be generated using the DAC

Table 5-10. UART Characteristics

over operating free-air temperature range (unless otherwise noted)

PARAMETER	MIN	TYP	MAX	UNIT
UART rate			3	MBaud

5.14 Peripheral Characteristics

5.14.1 ADC

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Table 5-11. Analog-to-Digital Converter (ADC) Characteristics

 $T_c = 25$ °C, $V_{DDS} = 3.0$ V and voltage scaling enabled, unless otherwise noted. (1) Performance numbers require use of offset and gain adjustements in software by TI-provided ADC drivers.

	PARAMETER	TEST CONDITIONS	MIN TYP	MAX	UNIT
	Input voltage range		0	VDDS	V
	Resolution		12		Bits
	Sample Rate			200	ksps
	Offset	Internal 4.3 V equivalent reference ⁽²⁾	-0.24		LSB
	Gain error	Internal 4.3 V equivalent reference ⁽²⁾	7.14		LSB
DNL ⁽³⁾	Differential nonlinearity		>-1		LSB
INL	Integral nonlinearity		±4		LSB
ENOR		Internal 4.3 V equivalent reference ⁽²⁾ , 200 kSamples/s, 9.6 kHz input tone	9.8		
		Internal 4.3 V equivalent reference ⁽²⁾ , 200 kSamples/s, 9.6 kHz input tone, DC/DC enabled	9.8		
		VDDS as reference, 200 kSamples/s, 9.6 kHz input tone	10.1		
ENOB	Effective number of bits	Internal reference, voltage scaling disabled, 32 samples average, 200 kSamples/s, 300 Hz input tone	11.1		Bits
		Internal reference, voltage scaling disabled, 14-bit mode, 200 kSamples/s, 300 Hz input tone (4)	11.3		
		Internal reference, voltage scaling disabled, 15-bit mode, 200 kSamples/s, 300 Hz input tone (4)	11.6		
	Total harmonic distortion	Internal 4.3 V equivalent reference ⁽²⁾ , 200 kSamples/s, 9.6 kHz input tone	-65		
THD		VDDS as reference, 200 kSamples/s, 9.6 kHz input tone	-70		Bits
		Internal reference, voltage scaling disabled, 32 samples average, 200 kSamples/s, 300 Hz input tone	-72		
	Signal-to-noise	Internal 4.3 V equivalent reference ⁽²⁾ , 200 kSamples/s, 9.6 kHz input tone	60		
SINAD, SNDR	and	VDDS as reference, 200 kSamples/s, 9.6 kHz input tone	63		dB
0.12.1	distortion ratio	Internal reference, voltage scaling disabled, 32 samples average, 200 kSamples/s, 300 Hz input tone	68		
		Internal 4.3 V equivalent reference (2), 200 kSamples/s, 9.6 kHz input tone	70		
SFDR	Spurious-free dynamic range	VDDS as reference, 200 kSamples/s, 9.6 kHz input tone	73		dB
		Internal reference, voltage scaling disabled, 32 samples average, 200 kSamples/s, 300 Hz input tone	75		
	Conversion time	Serial conversion, time-to-output, 24 MHz clock	50		Clock Cycles
	Current consumption	Internal 4.3 V equivalent reference (2)	0.42		mA
	Current consumption	VDDS as reference	0.6		mA
	Reference voltage	Equivalent fixed internal reference (input voltage scaling enabled). For best accuracy, the ADC conversion should be initiated through the TI-RTOS API in order to include the gain/offset compensation factors stored in FCFG1	4.3 ⁽²⁾⁽⁵⁾		V
	Reference voltage	Fixed internal reference (input voltage scaling disabled). For best accuracy, the ADC conversion should be initiated through the TI-RTOS API in order to include the gain/offset compensation factors stored in FCFG1. This value is derived from the scaled value (4.3 V) as follows: $V_{\text{ref}} = 4.3 \text{ V} \times 1408 \text{ / }4095$	1.48		V
	Reference voltage	VDDS as reference, input voltage scaling enabled	VDDS		V

- (1) Using IEEE Std 1241-2010 for terminology and test methods
- (2) Input signal scaled down internally before conversion, as if voltage range was 0 to 4.3 V
- (3) No missing codes
- 4) ADC_output = $\Sigma(4^n \text{ samples }) >> n$, n = desired extra bits
- (5) Applied voltage must be within Absolute Maximum Ratings (see Section 5.1) at all times



Table 5-11. Analog-to-Digital Converter (ADC) Characteristics (continued)

 $T_c = 25$ °C, $V_{DDS} = 3.0$ V and voltage scaling enabled, unless otherwise noted. (1)

Performance numbers require use of offset and gain adjustements in software by TI-provided ADC drivers.

PARAMETER	TEST CONDITIONS	MIN	TYP	MAX	UNIT
Reference voltage	VDDS as reference, input voltage scaling disabled		VDDS / 2.82 ⁽⁵⁾		V
Input impedance	200 kSamples/s, voltage scaling enabled. Capacitive input, Input impedance depends on sampling frequency and sampling time		>1		$M\Omega$

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5.14.2 DAC

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Table 5-12. Digital-to-Analog Converter (DAC) Characteristics

= 3.0 V unless otherwise noted T - 25 °C V

	PARAMETER	TEST CONDITIONS	MIN	TYP	MAX	UNIT	
eneral	Parameters						
	Resolution			8		Bits	
		Any load, any V _{REF} , pre-charge OFF, DAC charge-pump ON	1.8		3.8		
DDS	Supply voltage	External Load ⁽¹⁾ , any V _{REF} , pre-charge OFF, DAC charge-pump OFF	2.0		3.8	٧	
		Any load, V _{REF} = DCOUPL, pre-charge ON	2.6		3.8		
	Clask fraguency	Buffer ON (recommended for external load)	16		250	I/U-	
DAC	Clock frequency	Buffer OFF (internal load)	16		1000	kHz	
-	Valtage autout settling time	V _{REF} = VDDS, buffer OFF, internal load		13		4 / 5	
	Voltage output settling time	V _{REF} = VDDS, buffer ON, external capacitive load = 20 pF ⁽²⁾		13.8		1 / F _{DAC}	
	External capacitive load			20	200	pF	
	External resistive load		10			$M\Omega$	
	Short circuit current				400	μΑ	
Z _{MAX}		VDDS = 3.8 V, DAC charge-pump OFF		50.8			
		VDDS = 3.0 V, DAC charge-pump ON		51.7			
	Max output impedance Vref	VDDS = 3.0 V, DAC charge-pump OFF		53.2			
	= VDDS, buffer ON, CLK 250 kHz	VDDS = 2.0 V, DAC charge-pump ON		48.7		$k\Omega$	
		VDDS = 2.0 V, DAC charge-pump OFF		70.2			
		VDDS = 1.8 V, DAC charge-pump ON		46.3			
		VDDS = 1.8 V, DAC charge-pump OFF		88.9			
nternal	Load - Continuous Time Comp	parator / Low Power Clocked Comparator					
	Differential nonlinearity	V _{REF} = VDDS, load = Continuous Time Comparator or Low Power Clocked Comparator F _{DAC} = 250 kHz		±1		(3)	
ONL	Differential nonlinearity	V _{REF} = VDDS, load = Continuous Time Comparator or Low Power Clocked Comparator F _{DAC} = 16 kHz		±1.2		LSB ⁽³⁾	
		V _{REF} = VDDS = 3.8 V		±0.64			
		V _{REF} = VDDS = 3.0 V		±0.81			
	Offset error ⁽⁴⁾	V _{REF} = VDDS = 1.8 V		±1.27		. 05 (3)	
	Load = Continuous Time Comparator	V _{REF} = DCOUPL, pre-charge ON		±3.43		LSB ⁽³⁾	
	'	V _{REF} = DCOUPL, pre-charge OFF		±2.88			
		V _{REF} = ADCREF		±2.37			
		V _{REF} = VDDS = 3.8 V		±0.78			
		V _{REF} = VDDS = 3.0 V		±0.77			
	Offset error ⁽⁴⁾	V _{REF} = VDDS = 1.8 V		±3.46		(2)	
	Load = Low Power Clocked Comparator	V _{REF} = DCOUPL, pre-charge ON		±3.44		LSB ⁽³⁾	
	o mparator	V _{REF} = DCOUPL, pre-charge OFF		±4.70			
		V _{REF} = ADCREF		±4.11			
		V _{REF} = VDDS = 3.8 V		±1.53			
		V _{REF} = VDDS = 3.0 V		±1.71			
	Max code output voltage variation (4)	V _{RFF} = VDDS = 1.8 V		±2.10		,	
	Load = Continuous Time	V _{RFF} = DCOUPL, pre-charge ON		±6.00		LSB ⁽³⁾	
	Comparator	V _{REF} = DCOUPL, pre-charge OFF		±3.85			
		V _{REF} = ADCREF					

 ⁽¹⁾ Keysight 34401A Multimeter
 (2) A load > 20 pF will increases the settling time
 (3) 1 LSB (V_{REF} 3.8 V/3.0 V/1.8 V/DCOUPL/ADCREF) = 14.10 mV/11.13 mV/6.68 mV/4.67 mV/5.48 mV

Includes comparator offset



Table 5-12. Digital-to-Analog Converter (DAC) Characteristics (continued)

 $T_c = 25$ °C, $V_{DDS} = 3.0$ V, unless otherwise noted.

	PARAMETER	TEST CONDITIONS	MIN TYP	MAX	UNIT
		V _{REF} = VDDS = 3.8 V	±2.92		
	Man and antoni coltano	V _{REF} =VDDS = 3.0 V	±3.06		
	Max code output voltage variation (4)	V _{REF} = VDDS = 1.8 V	±3.91		LSB ⁽³⁾
	Load = Low Power Clocked	V _{REF} = DCOUPL, pre-charge ON	±7.84		LSB
	Comparator	V _{REF} = DCOUPL, pre-charge OFF	±4.06		
		V _{REF} = ADCREF	±6.94		
		V _{REF} = VDDS = 3.8 V, code 1	0.03		
		V _{REF} = VDDS = 3.8 V, code 255	3.62		
		V _{REF} = VDDS = 3.0 V, code 1	0.02		
		V _{REF} = VDDS = 3.0 V, code 255	2.86		
		V _{REF} = VDDS = 1.8 V, code 1	0.01		
	Output voltage range (4)	V _{REF} = VDDS = 1.8 V, code 255	1.71		
	Load = Continuous Time Comparator	V _{REF} = DCOUPL, pre-charge OFF, code 1	0.01		V
	o o parator	V _{REF} = DCOUPL, pre-charge OFF, code 255	1.21		
		V _{REF} = DCOUPL, pre-charge ON, code 1	1.27		
		V _{REF} = DCOUPL, pre-charge ON, code 255	2.46		
		V _{REF} = ADCREF, code 1	0.01		
		V _{REF} = ADCREF, code 255	1.41		
		$V_{REF} = VDDS = 3.8 \text{ V, code 1}$	0.03		
		V _{REF} = VDDS = 3.8 V, code 255	3.61		
		V _{REF} = VDDS = 3.0 V, code 1	0.02		
		V _{REF} = VDDS = 3.0 V, code 255	2.85		
		V _{REF} = VDDS = 1.8 V, code 1	0.01		
	Output voltage range (4)	V _{REF} = VDDS = 1.8 V, code 255	1.71		
	Load = Low Power Clocked	V _{RFF} = DCOUPL, pre-charge OFF, code 1	0.01		V
	Comparator	$V_{RFF} = DCOUPL$, pre-charge OFF, code 255	1.21		
		V_{REF} = DCOUPL, pre-charge ON, code 1	1.27		
		$V_{REF} = DCOUPL$, pre-charge ON, code 255	2.46		
		$V_{REF} = ADCREF$, code 1	0.01		
		$V_{REF} = ADCREF$, code 255	1.41		
torns	al Load (Keysight 34401A Mult		1.41		
terne	I Load (Neysight 34401A Mult	$V_{REF} = VDDS$, $F_{DAC} = 250 \text{ kHz}$	±1		
L	Intogral poplingarity	$V_{REF} = V_{DAC} + V_{DAC} = 250 \text{ kHz}$ $V_{REF} = DCOUPL, F_{DAC} = 250 \text{ kHz}$	±1		LSB ⁽³⁾
L	Integral nonlinearity				LOD
JL.	Differential poplings with	$V_{REF} = ADCREF, F_{DAC} = 250 \text{ kHz}$	±1		LSB ⁽³⁾
NL.	Differential nonlinearity	$V_{REF} = VDDS$, $F_{DAC} = 250 \text{ kHz}$ $V_{REF} = VDDS = 3.8 \text{ V}$	±1 ±0.20		LSB
		$V_{REF} = VDDS = 3.0 V$	±0.25		
	Offset error	$V_{REF} = VDDS = 1.8 \text{ V}$	±0.45		LSB(3)
		V _{REF} = DCOUPL, pre-charge ON	±1.55		
		V _{REF} = DCOUPL, pre-charge OFF	±1.30		
		V _{REF} = ADCREF	±1.10		
		$V_{REF} = VDDS = 3.8 V$	±0.60		
		$V_{REF} = VDDS = 3.0 \text{ V}$	±0.55		
Max code output voltage variation	V _{REF} = VDDS = 1.8 V	±0.60		LSB ⁽³⁾	
	V _{REF} = DCOUPL, pre-charge ON	±3.45		_00	
		V _{REF} = DCOUPL, pre-charge OFF	±2.10		
		V _{REF} = ADCREF	±1.90		

Table 5-12. Digital-to-Analog Converter (DAC) Characteristics (continued)

 T_c = 25 °C, V_{DDS} = 3.0 V, unless otherwise noted.

PARAMETER	TEST CONDITIONS	MIN TYP	MAX	UNIT
	V _{REF} = VDDS = 3.8 V, code 1	0.03		
	V _{REF} = VDDS = 3.8 V, code 255	3.61		
	V _{REF} = VDDS = 3.0 V, code 1	0.02		
	V _{REF} = VDDS = 3.0 V, code 255	2.85		
	V _{REF} = VDDS = 1.8 V, code 1	0.02		
Output voltage range	V _{REF} = VDDS = 1.8 V, code 255	1.71		V
Load = Low Power Clocked Comparator	V _{REF} = DCOUPL, pre-charge OFF, code 1	0.02		V
	V _{REF} = DCOUPL, pre-charge OFF, code 255	1.20		
	V _{REF} = DCOUPL, pre-charge ON, code 1	1.27		
	V _{REF} = DCOUPL, pre-charge ON, code 255	2.46		
	V _{REF} = ADCREF, code 1	0.02		
	V _{REF} = ADCREF, code 255	1.42		



5.14.3 Temperature and Battery Monitor

Table 5-13. Temperature Sensor

Measured on a Texas Instruments reference design with $T_c = 25$ °C, $V_{DDS} = 3.0$ V, unless otherwise noted.

PARAMETER	TEST CONDITIONS	MIN	TYP MAX	UNIT
Resolution			2	°C
Accuracy	-40 °C to 0 °C		±4.0	°C
Accuracy	0 °C to 105 °C		±2.5	°C
Supply voltage coefficient ⁽¹⁾			3.6	°C/V

⁽¹⁾ The temperature sensor is automatically compensated for VDDS variation when using the TI-provided driver.

Table 5-14. Battery Monitor

Measured on a Texas Instruments reference design with T_c = 25 °C, unless otherwise noted.

PARAMETER	TEST CONDITIONS	MIN	TYP	MAX	UNIT
Resolution			25		mV
Range		1.8	·	3.8	V
Integral nonlinearity (max)			23		mV
Accuracy	VDDS = 3.0 V		22.5		mV
Offset error			-32		mV
Gain error			-1		%



5.14.4 Comparators

Table 5-15. Low-Power Clocked Comparator

 $T_c = 25$ °C, $V_{DDS} = 3.0$ V, unless otherwise noted.

- C = C, TDDS = C T, annece care meeting.							
PARAMETER	TEST CONDITIONS	MIN	TYP	MAX	UNIT		
Input voltage range		0		V_{DDS}	V		
Clock frequency			SCLK_LF				
Internal reference voltage ⁽¹⁾	Using internal DAC with VDDS as reference voltage, DAC code = 0 - 255	0.02	24 - 2.865		V		
Offset	Measured at V _{DDS} / 2, includes error from internal DAC		±5		mV		
Decision time	Step from -50 mV to 50 mV	·	1		Clock Cycle		

⁽¹⁾ The comparator can use an internal 8 bits DAC as its reference. The DAC output voltage range depends on the reference voltage selected. See Table 5-12

5.14.5 Current Source

Table 5-16. Programmable Current Source

 T_c = 25 °C, V_{DDS} = 3.0 V, unless otherwise noted.

PARAMETER	TEST CONDITIONS	MIN	TYP	MAX	UNIT
Current source programmable output range (logarithmic range)			0.25 - 20		μΑ
Resolution			0.25		μΑ

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5.14.6 GPIO

Table 5-17. GPIO DC Characteristics

PARAMETER	TEST CONDITIONS	MIN TYP	MAX	UNIT
T _A = 25 °C, V _{DDS} = 1.8 V		1		
GPIO VOH at 8 mA load	IOCURR = 2, high-drive GPIOs only	1.56		V
GPIO VOL at 8 mA load	IOCURR = 2, high-drive GPIOs only	0.24		V
GPIO VOH at 4 mA load	IOCURR = 1	1.59		V
GPIO VOL at 4 mA load	IOCURR = 1	0.21		V
GPIO pullup current	Input mode, pullup enabled, Vpad = 0 V	73		μA
GPIO pulldown current	Input mode, pulldown enabled, Vpad = VDDS	19		μΑ
GPIO low-to-high input transition, with hysteresis	IH = 1, transition voltage for input read as $0 \rightarrow 1$	1.08		V
GPIO high-to-low input transition, with hysteresis	IH = 1, transition voltage for input read as $1 \rightarrow 0$	0.73		V
GPIO input hysteresis	$IH = 1$, difference between $0 \rightarrow 1$ and $1 \rightarrow 0$ points	0.35		٧
T _A = 25 °C, V _{DDS} = 3.0 V		1		
GPIO VOH at 8 mA load	IOCURR = 2, high-drive GPIOs only	2.59		V
GPIO VOL at 8 mA load	IOCURR = 2, high-drive GPIOs only	0.42		V
GPIO VOH at 4 mA load	IOCURR = 1	2.63		V
GPIO VOL at 4 mA load	IOCURR = 1	0.40		V
T _A = 25 °C, V _{DDS} = 3.8 V		<u> </u>		
GPIO pullup current	Input mode, pullup enabled, Vpad = 0 V	282		μA
GPIO pulldown current	Input mode, pulldown enabled, Vpad = VDDS	110		μA
GPIO low-to-high input transition, with hysteresis	IH = 1, transition voltage for input read as $0 \rightarrow 1$	1.97		V
GPIO high-to-low input transition, with hysteresis	IH = 1, transition voltage for input read as $1 \rightarrow 0$	1.55		V
GPIO input hysteresis	IH = 1, difference between $0 \rightarrow 1$ and $1 \rightarrow 0$ points	0.42		٧
T _A = 25 °C				
VIH	Lowest GPIO input voltage reliably interpreted as a High	0.8*V _{DDS}		V
VIL	Highest GPIO input voltage reliably interpreted as a Low		0.2*V _{DDS}	V



5.15 Typical Characteristics

All measurements in this section are done with T_c = 25 °C and V_{DDS} = 3.0 V, unless otherwise noted. See *Recommended Operating Conditions*, Section 5.3, for device limits. Values exceeding these limits are for reference only.

5.15.1 MCU Current

Active Current vs. VDDS Running CoreMark, SCLK_HF = 48 MHz RCOSC

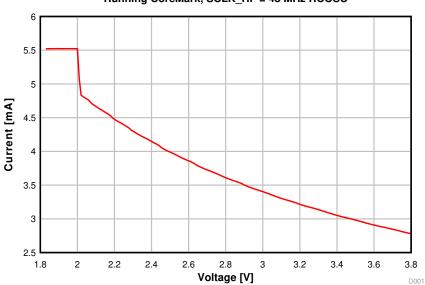


Figure 5-4. Active Mode (MCU) Current vs. Supply Voltage (VDDS)

Standby Current vs. Temperature 80 kB RAM Retention, no Cache Retention, RTC On SCLK_LF = 32 kHz XOSC

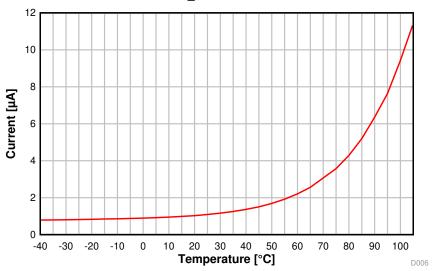


Figure 5-5. Standby Mode (MCU) Current vs. Temperature



5.15.2 RX Current

RX Current vs. Temperature BLE 1 Mbps, 2.44 GHz

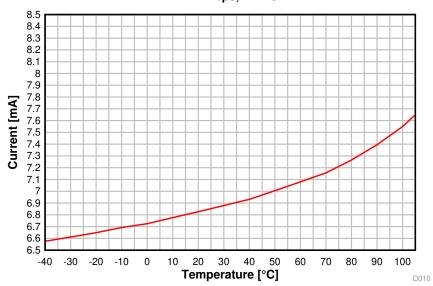


Figure 5-6. RX Current vs. Temperature (BLE 1 Mbps, 2.44 GHz)

RX Current vs. VDDS BLE 1 Mbps, 2.44 GHz

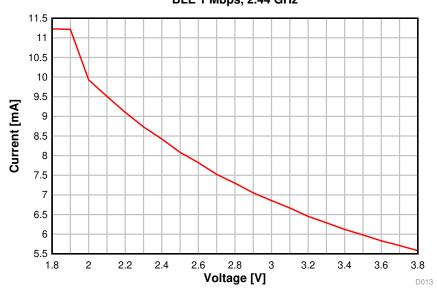


Figure 5-7. RX Current vs. Supply Voltage (VDDS) (BLE 1 Mbps, 2.44 GHz)

5.15.3 TX Current

TX Current vs. Temperature BLE 1 Mbps, 2.44 GHz, 0 dBm

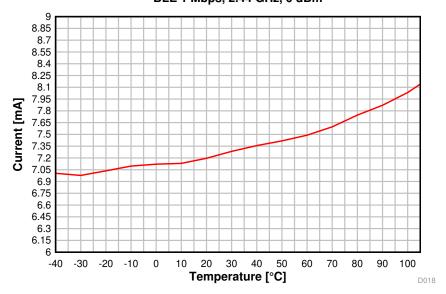


Figure 5-8. TX Current vs. Temperature (BLE 1 Mbps, 2.44 GHz)

TX Current vs. Temperature

BLE 1 Mbps, 2.44 GHz, +20 dBm PA, VDDS = 3.3 V

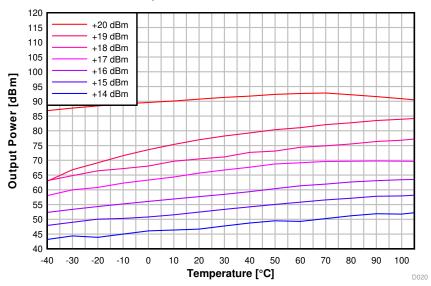


Figure 5-9. TX Current vs.
Temperature (BLE 1 Mbps, 2.44 GHz, VDDS = 3.3 V)



TX Current vs. Temperature
IEEE 802.15.4 (OQPSK DSSS1:8, 250 kbps), 2.44 GHz, +10 dBm PA

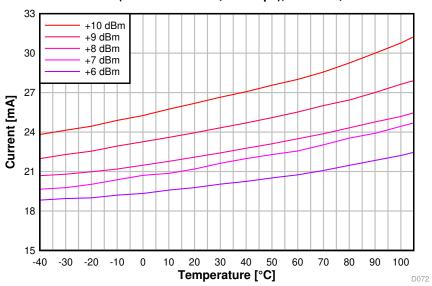
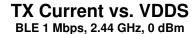


Figure 5-10. TX Current vs. Temperature (250 kbps, 2.44 GHz, +10 dBm PA)



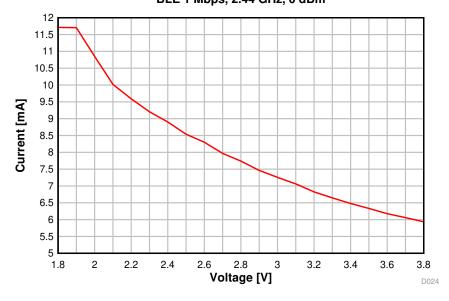


Figure 5-11. TX Current vs. Supply Voltage (VDDS) (BLE 1 Mbps, 2.44 GHz)

TX Current vs. VDDS BLE 1 Mbps, 2.44 GHz, +20 dBm PA

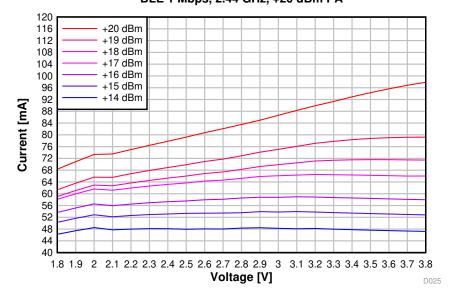


Figure 5-12. TX Current vs.
Supply Voltage (VDDS) (BLE 1 Mbps, 2.44 GHz, +20 dBm PA)

TX Current vs. VDDS IEEE 802.15.4 (OQPSK DSSS1:8, 250 kbps), 2.44 GHz, +10 dBm PA

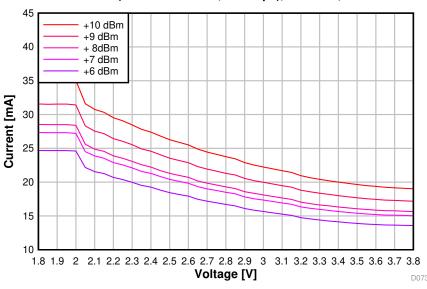


Figure 5-13. TX Current vs. Supply Voltage (VDDS) (250 kbps, 2.44 GHz, +10 dBm PA)

Table 5-18 shows typical TX current and output power for different output power settings.

Table 5-18. Typical TX Current and Output Power

	CC2652P at 2.4 GHz, VDDS = 3.0 V (Measured on CC1352PEM-XD7793-XD24-PA24)											
txPower	TX Power Setting (SmartRF Studio)	Typical Output Power [dBm]	Typical Current Consumption [mA]									
0x7217	5	3.1	8.7									
0x4E63	4	1.8	8.2									
0x385D	3	0.5	7.7									
0x3259	2	-0.7	7.3									
0x2856	1	-1.8	6.9									
0x2853	0	-3.1	6.6									
0x12D6	-5	-7.7	5.8									
0x0ACF	-10	-12.6	5.3									
0x06CA	-15	-17.9	4.9									
0x04C6	-20	-23.6	4.7									

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5.15.4 RX Performance

Sensitivity vs. Frequency BLE 1 Mbps, 2.44 GHz

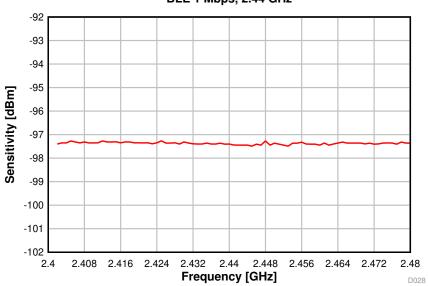


Figure 5-14. Sensitivity vs. Frequency (BLE 1 Mbps, 2.44 GHz)

Sensitivity vs. Frequency IEEE 802.15.4 (OQPSK DSSS1:8, 250 kbps)

-95 -96 -97 -98 Sensitivity [dBm] -99 -100 -101 -102 -103 -104 -105

Figure 5-15. Sensitivity vs. Frequency (250 kbps, 2.44 GHz)

2.44

Frequency [GHz]

2.448

2.456 2.464 2.472

2.432

2.424

2.4

2.408 2.416

2.48

Sensitivity vs. Temperature BLE 1 Mbps, 2.44 GHz

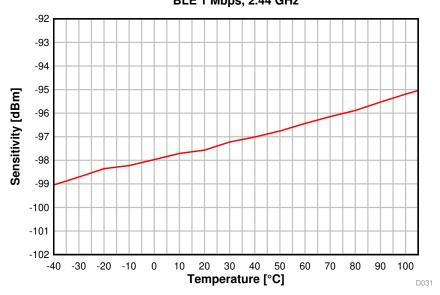


Figure 5-16. Sensitivity vs. Temperature (BLE 1 Mbps, 2.44 GHz)

Sensitivity vs. Temperature IEEE 802.15.4 (OQPSK DSSS1:8, 250 kbps), 2.44 GHz

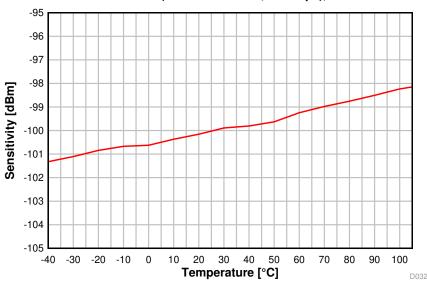


Figure 5-17. Sensitivity vs. Temperature (250 kbps, 2.44 GHz)

-92 -93 -94 -95

-96 -97 -98 -99 -100 -101 -102 1.8

2

2.2

2.4

Sensitivity [dBm]

Sensitivity vs. VDDS BLE 1 Mbps, 2.44 GHz

DEL I MOPS, 2.44 GIZ

Figure 5-18. Sensitivity vs. Supply Voltage (VDDS) (BLE 1 Mbps, 2.44 GHz)

2.6

Sensitivity vs. VDDS BLE 1 Mbps, 2.44 GHz, DCDC Off

2.8

Voltage [V]

3

3.2

3.4

3.6

3.8

D034

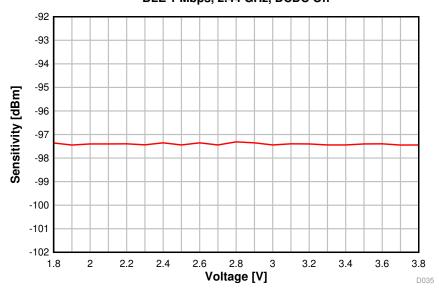


Figure 5-19. Sensitivity vs. Supply Voltage (VDDS) (BLE 1 Mbps, 2.44 GHz, DCDC Off)

Sensitivity vs. VDDS

IEEE 802.15.4 (OQPSK DSSS1:8, 250 kbps), 2.44 GHz

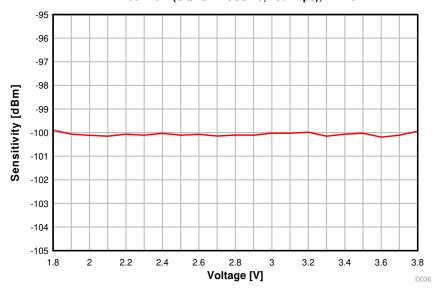


Figure 5-20. Sensitivity vs. Supply Voltage (VDDS) (250 kbps, 2.44 GHz)

5.15.5 TX Performance

Output Power vs. Temperature

BLE 1 Mbps, 2.44 GHz, 0 dBm

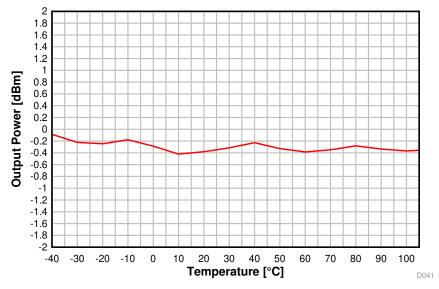


Figure 5-21. Output Power vs. Temperature (BLE 1 Mbps, 2.44 GHz)

Output Power vs. Temperature BLE 1 Mbps, 2.44 GHz, +5 dBm

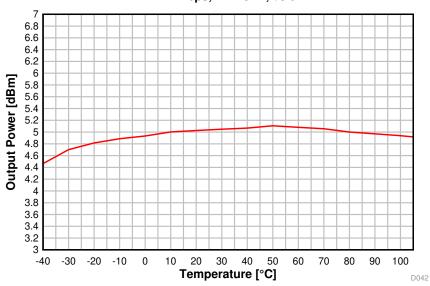


Figure 5-22. Output Power vs. Temperature (BLE 1 Mbps, 2.44 GHz, +5 dBm)

Output Power vs. Temperature

BLE 1 Mbps, 2.44 GHz, +20 dBm PA, VDDS = 3.3 V

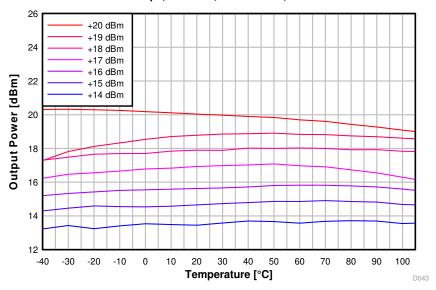


Figure 5-23. Output Power vs. Temperature (BLE 1 Mbps, 2.44 GHz, +20 dBm PA)

Output Power vs. Temperature IEEE 802.15.4 (OQPSK DSSS1:8, 250 kbps), 2.44 GHz, +10 dBm PA

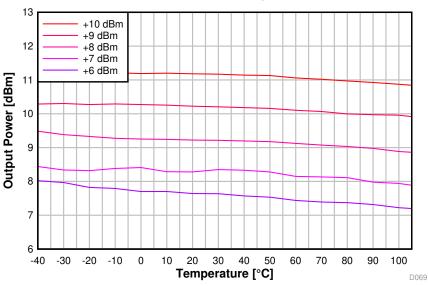


Figure 5-24. Output Power vs. Temperature (2.44 GHz, +10 dBm PA)

Output Power vs. VDDS

BLE 1 Mbps, 2.44 GHz, 0 dBm

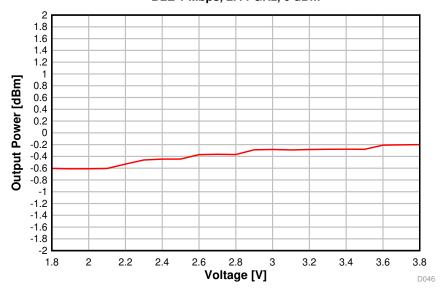


Figure 5-25. Output Power vs. Supply Voltage (VDDS) (BLE 1 Mbps, 2.44 GHz)

Output power vs. VDDS

BLE 1 Mbps, 2.44 GHz, +5 dBm

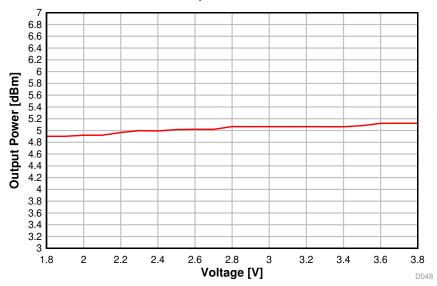


Figure 5-26. Output Power vs. Supply Voltage (VDDS) (BLE 1 Mbps, 2.44 GHz, +5 dBm)



Output power vs. VDDS BLE 1 Mbps, 2.44 GHz, +20 dBm PA

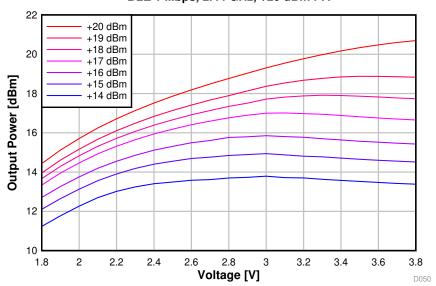


Figure 5-27. Output Power vs. Supply Voltage (VDDS) (BLE 1 Mbps, 2.44 GHz, +20 dBm PA)

Output Power vs. VDDS IEEE 802.15.4 (OQPSK DSSS1:8, 250 kbps), 2.44 GHz, +10 dBm PA

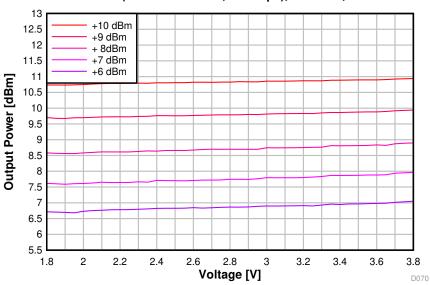


Figure 5-28. Output Power vs. Supply Voltage (VDDS) (2.44 GHz, +10 dBm PA)

Output Power vs. Frequency BLE 1 Mbps, 2.44 GHz, 0 dBm

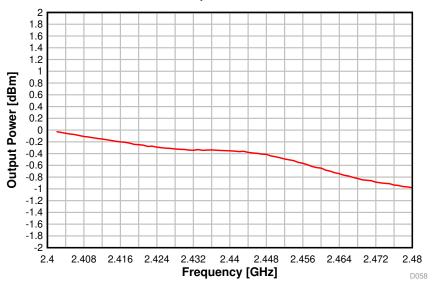


Figure 5-29. Output Power vs. Frequency (BLE 1 Mbps, 2.44 GHz)

Output Power vs. Frequency

BLE 1 Mbps, 2.44 GHz, +5 dBm

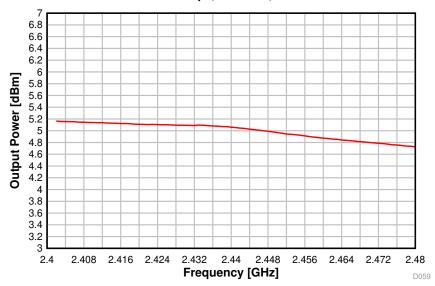


Figure 5-30. Output Power vs. Frequency (BLE 1 Mbps, 2.44 GHz, +5 dBm)

Output Power vs. Frequency BLE 1 Mbps, +20 dBm PA, VDDS = 3.3 V

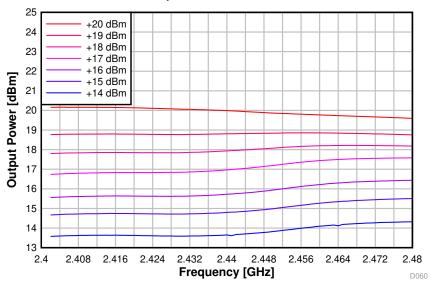


Figure 5-31. Output Power vs. Frequency (BLE 1 Mbps, 2.44 GHz, +20 dBm PA)

Output Power vs. Frequency IEEE 802.15.4 (OQPSK DSSS1:8, 250 kbps), +10 dBm PA

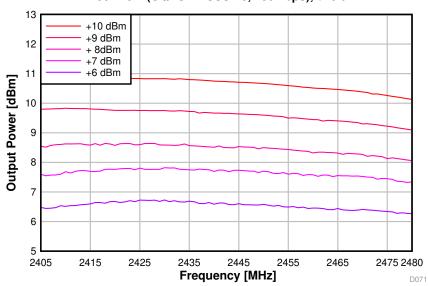


Figure 5-32. Output Power vs. Frequency (250 kbps, +10 dBm PA)

5.15.6 ADC Performance

ENOB vs. Input Frequency

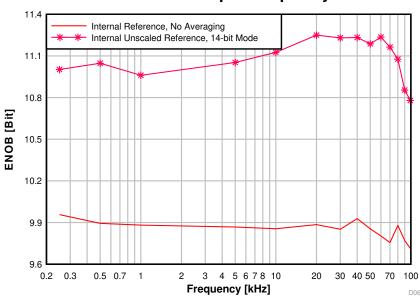


Figure 5-33. ENOB vs. Input Frequency

ENOB vs. Sampling Frequency

Vin = 3.0 V Sine wave, Internal reference, Fin = Fs / 10

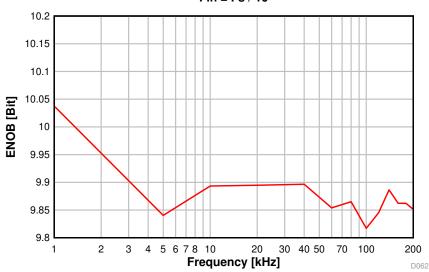


Figure 5-34. ENOB vs. Sampling Frequency

INL vs. ADC Code

Vin = 3.0 V Sine wave, Internal reference, 200 kSamples/s

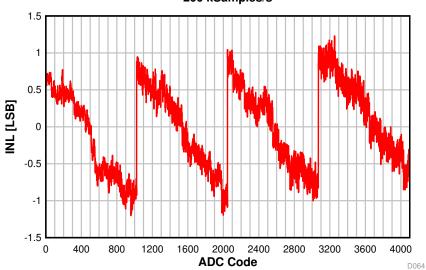


Figure 5-35. INL vs. ADC Code

DNL vs. ADC Code

Vin = 3.0 V Sine wave, Internal reference, 200 kSamples/s

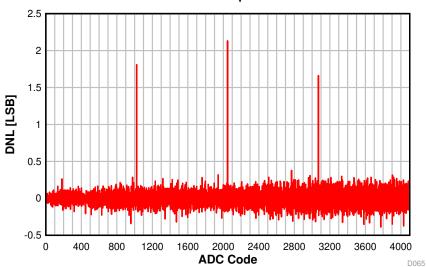


Figure 5-36. DNL vs. ADC Code

ADC Accuracy vs. Temperature Vin = 1 V, Internal reference,

200 kSamples/s

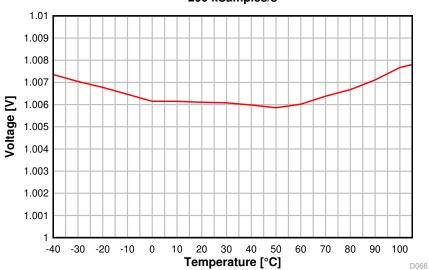


Figure 5-37. ADC Accuracy vs. **Temperature**

ADC Accuracy vs. VDDS

Vin = 1 V, Internal reference, 200 kSamples/s

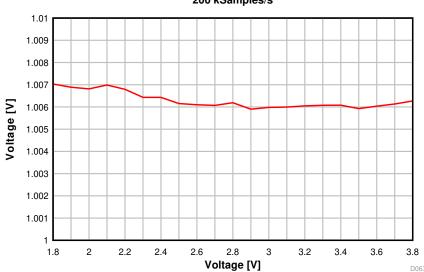


Figure 5-38. ADC Accuracy vs. Supply Voltage (VDDS)



6 Detailed Description

6.1 Overview

Section 1.4 shows the core modules of the CC2652P device.

6.2 System CPU

The CC2652P SimpleLink[™] Wireless MCU contains an Arm[®] Cortex[®]-M4F system CPU, which runs the application and the higher layers of radio protocol stacks.

The system CPU is the foundation of a high-performance, low-cost platform that meets the system requirements of minimal memory implementation, and low-power consumption, while delivering outstanding computational performance and exceptional system response to interrupts.

Its features include the following:

- ARMv7-M architecture optimized for small-footprint embedded applications
- Arm Thumb[®]-2 mixed 16- and 32-bit instruction set delivers the high performance expected of a 32-bit Arm core in a compact memory size
- · Fast code execution permits increased sleep mode time
- Deterministic, high-performance interrupt handling for time-critical applications
- Single-cycle multiply instruction and hardware divide
- Hardware division and fast digital-signal-processing oriented multiply accumulate
- · Saturating arithmetic for signal processing
- IEEE 754-compliant single-precision Floating Point Unit (FPU)
- Memory Protection Unit (MPU) for safety-critical applications
- Full debug with data matching for watchpoint generation
 - Data Watchpoint and Trace Unit (DWT)
 - JTAG Debug Access Port (DAP)
 - Flash Patch and Breakpoint Unit (FPB)
- Trace support reduces the number of pins required for debugging and tracing
 - Instrumentation Trace Macrocell Unit (ITM)
 - Trace Port Interface Unit (TPIU) with asynchronous serial wire output (SWO)
- Optimized for single-cycle flash memory access
- Tightly connected to 8-KB 4-way random replacement cache for minimal active power consumption and wait states
- Ultra-low-power consumption with integrated sleep modes
- 48 MHz operation
- 1.25 DMIPS per MHz

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6.3 Radio (RF Core)

The RF Core is a highly flexible and future proof radio module which contains an Arm Cortex-M0 processor that interfaces the analog RF and base-band circuitry, handles data to and from the system CPU side, and assembles the information bits in a given packet structure. The RF core offers a high level, command-based API to the main CPU that configurations and data are passed through. The Arm Cortex-M0 processor is not programmable by customers and is interfaced through the TI-provided RF driver that is included with the SimpleLink Software Development Kit (SDK).

The RF core can autonomously handle the time-critical aspects of the radio protocols, thus offloading the main CPU, which reduces power and leaves more resources for the user application. Several signals are also available to control external circuitry such as RF switches or range extenders autonomously.

Multiprotocol solutions are enabled through time-sliced access of the radio, handled transparently for the application through the TI-provided RF driver and dual-mode manager.

The various physical layer radio formats are partly built as a software defined radio where the radio behavior is either defined by radio ROM contents or by non-ROM radio formats delivered in form of firmware patches with the SimpleLink SDKs. This allows the radio platform to be updated for support of future versions of standards even with over-the-air (OTA) updates while still using the same silicon.

6.3.1 Bluetooth 5 low energy

The RF Core offers full support for Bluetooth 5 low energy, including the high-sped 2-Mbps physical layer and the 500-kbps and 125-kbps long range PHYs (Coded PHY) through the TI provided Bluetooth 5 stack or through a high-level Bluetooth API. The Bluetooth 5 PHY and part of the controller are in radio and system ROM, providing significant savings in memory usage and more space available for applications.

The new high-speed mode allows data transfers up to 2 Mbps, twice the speed of Bluetooth 4.2 and five times the speed of Bluetooth 4.0, without increasing power consumption. In addition to faster speeds, this mode offers significant improvements for energy efficiency and wireless coexistence with reduced radio communication time.

Bluetooth 5 also enables unparalleled flexibility for adjustment of speed and range based on application needs, which capitalizes on the high-speed or long-range modes respectively. Data transfers are now possible at 2 Mbps, enabling development of applications using voice, audio, imaging, and data logging that were not previously an option using Bluetooth low energy. With high-speed mode, existing applications deliver faster responses, richer engagement, and longer battery life. Bluetooth 5 enables fast, reliable firmware updates.

6.3.2 802.15.4 (Thread, Zigbee, 6LoWPAN)

Through a dedicated IEEE radio API, the RF Core supports the 2.4-GHz IEEE 802.15.4-2011 physical layer (2 Mchips per second Offset-QPSK with DSSS 1:8), used in Thread, Zigbee, and 6LoWPAN protocols. The 802.15.4 PHY and MAC are in radio and system ROM. TI also provides royalty-free protocol stacks for Thread and Zigbee as part of the SimpleLink SDK, enabling a robust end-to-end solution.



6.4 Memory

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The up to 352-KB nonvolatile (Flash) memory provides storage for code and data. The flash memory is insystem programmable and erasable. The last flash memory sector must contain a Customer Configuration section (CCFG) that is used by boot ROM and TI provided drivers to configure the device. This configuration is done through the ccfq.c source file that is included in all TI provided examples.

The ultra-low leakage system static RAM (SRAM) is split into up to five 16-KB blocks and can be used for both storage of data and execution of code. Retention of SRAM contents in Standby power mode is enabled by default and included in Standby mode power consumption numbers. Parity checking for detection of bit errors in memory is built-in, which reduces chip-level soft errors and thereby increases reliability. System SRAM is always initialized to zeroes upon code execution from boot.

To improve code execution speed and lower power when executing code from nonvolatile memory, a 4way nonassociative 8-KB cache is enabled by default to cache and prefetch instructions read by the system CPU. The cache can be used as a general-purpose RAM by enabling this feature in the Customer Configuration Area (CCFG).

There is a 4-KB ultra-low leakage SRAM available for use with the Sensor Controller Engine which is typically used for storing Sensor Controller programs, data and configuration parameters. This RAM is also accessible by the system CPU. The Sensor Controller RAM is not cleared to zeroes between system resets.

The ROM includes a TI-RTOS kernel and low-level drivers, as well as significant parts of selected radio stacks, which frees up flash memory for the application. The ROM also contains a serial (SPI and UART) bootloader that can be used for initial programming of the device.

6.5 Sensor Controller

The Sensor Controller contains circuitry that can be selectively enabled in both Standby and Active power modes. The peripherals in this domain can be controlled by the Sensor Controller Engine, which is a proprietary power-optimized CPU. This CPU can read and monitor sensors or perform other tasks autonomously; thereby significantly reducing power consumption and offloading the system CPU.

The Sensor Controller Engine is user programmable with a simple programming language that has syntax similar to C. This programmability allows for sensor polling and other tasks to be specified as sequential algorithms rather than static configuration of complex peripheral modules, timers, DMA, register programmable state machines, or event routing.

The main advantages are:

- · Flexibility data can be read and processed in unlimited manners while still ensuring ultra-low power
- 2 MHz low-power mode enables lowest possible handling of digital sensors
- Dynamic reuse of hardware resources
- 40-bit accumulator supporting multiplication, addition and shift
- Observability and debugging options

Sensor Controller Studio is used to write, test, and debug code for the Sensor Controller. The tool produces C driver source code, which the System CPU application uses to control and exchange data with the Sensor Controller. Typical use cases may be (but are not limited to) the following:

- · Read analog sensors using integrated ADC or comparators
- Interface digital sensors using GPIOs, SPI, UART, or I²C (UART and I²C are bit-banged)
- · Capacitive sensing
- · Waveform generation
- Very low-power pulse counting (flow metering)
- Key scan

The peripherals in the Sensor Controller include the following:

- The low-power clocked comparator can be used to wake the system CPU from any state in which the
 comparator is active. A configurable internal reference DAC can be used in conjunction with the
 comparator. The output of the comparator can also be used to trigger an interrupt or the ADC.
- Capacitive sensing functionality is implemented through the use of a constant current source, a time-to-digital converter, and a comparator. The continuous time comparator in this block can also be used as a higher-accuracy alternative to the low-power clocked comparator. The Sensor Controller takes care of baseline tracking, hysteresis, filtering, and other related functions when these modules are used for capacitive sensing.
- The ADC is a 12-bit, 200-ksamples/s ADC with eight inputs and a built-in voltage reference. The ADC can be triggered by many different sources including timers, I/O pins, software, and comparators.
- The analog modules can connect to up to eight different GPIOs
- Dedicated SPI master with up to 6 MHz clock speed

The peripherals in the Sensor Controller can also be controlled from the main application processor.



6.6 Cryptography

The CC2652P device comes with a wide set of modern cryptography-related hardware accelerators, drastically reducing code footprint and execution time for cryptographic operations. It also has the benefit of being lower power and improves availability and responsiveness of the system because the cryptography operations runs in a background hardware thread.

Together with a large selection of open-source cryptography libraries provided with the Software Development Kit (SDK), this allows for secure and future proof IoT applications to be easily built on top of the platform. The hardware accelerator modules are:

- True Random Number Generator (TRNG) module provides a true, nondeterministic noise source for the purpose of generating keys, initialization vectors (IVs), and other random number requirements.
 The TRNG is built on 24 ring oscillators that create unpredictable output to feed a complex nonlinearcombinatorial circuit.
- Secure Hash Algorithm 2 (SHA-2) with support for SHA224, SHA256, SHA384, and SHA512
- Advanced Encryption Standard (AES) with 128 and 256 bit key lengths
- Public Key Accelerator Hardware accelerator supporting mathematical operations needed for elliptic curves up to 512 bits and RSA key pair generation up to 1024 bits.

Through use of these modules and the TI provided cryptography drivers, the following capabilities are available for an application or stack:

Key Agreement Schemes

- Elliptic curve Diffie—Hellman with static or ephemeral keys (ECDH and ECDHE)
- Elliptic curve Password Authenticated Key Exchange by Juggling (ECJ-PAKE)

Signature Generation

Elliptic curve Diffie-Hellman Digital Signature Algorithm (ECDSA)

Curve Support

- Short Weierstrass form (full hardware support), such as:
 - NIST-P224, NIST-P256, NIST-P384, NIST-P521
 - Brainpool-256R1, Brainpool-384R1, Brainpool-512R1
 - secp256r1
- Montgomery form (hardware support for multiplication), such as:
 - Curve25519

SHA2 based MACs

- HMAC with SHA224, SHA256, SHA384, or SHA512
- Block cipher mode of operation
 - AESCCM
 - AESGCM
 - AESECB
 - AESCBC
 - AESCBC-MAC

True random number generation

Other capabilities, such as RSA encryption and signatures as well as Edwards type of elliptic curves such as Curve1174 or Ed25519, can also be implemented using the provided hardware accelerators but are not part of the TI SimpleLink SDK for the CC2652P device.

Product Folder Links: CC2652P

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6.7 Timers

A large selection of timers are available as part of the CC2652P device. These timers are:

Real-Time Clock (RTC)

A 70-bit 3-channel timer running on the 32 kHz low frequency system clock (SCLK_LF) This timer is available in all power modes except Shutdown. The timer can be calibrated to compensate for frequency drift when using the LF RCOSC as the low frequency system clock. If an external LF clock with frequency different from 32.768 kHz is used, the RTC tick speed can be adjusted to compensate for this. When using TI-RTOS, the RTC is used as the base timer in the operating system and should thus only be accessed through the kernel APIs such as the Clock module. The real time clock can also be read by the Sensor Controller Engine to timestamp sensor data and also has dedicated capture channels. By default, the RTC halts when a debugger halts the device.

General Purpose Timers (GPTIMER)

The four flexible GPTIMERs can be used as either 4x 32 bit timers or 8x 16 bit timers, all running on up to 48 MHz. Each of the 16- or 32-bit timers support a wide range of features such as one-shot or periodic counting, pulse width modulation (PWM), time counting between edges and edge counting. The inputs and outputs of the timer are connected to the device event fabric, which allows the timers to interact with signals such as GPIO inputs, other timers, DMA and ADC. The GPTIMERs are available in Active and Idle power modes.

Sensor Controller Timers

The Sensor Controller contains 3 timers:

AUX Timer 0 and 1 are 16-bit timers with a 2^N prescaler. Timers can either increment on a clock or on each edge of a selected tick source. Both one-shot and periodical timer modes are available.

AUX Timer 2 is a 16-bit timer that can operate at 24 MHz, 2 MHz or 32 kHz independent of the Sensor Controller functionality. There are 4 capture or compare channels, which can be operated in one-shot or periodical modes. The timer can be used to generate events for the Sensor Controller Engine or the ADC, as well as for PWM output or waveform generation.

Radio Timer

A multichannel 32-bit timer running at 4 MHz is available as part of the device radio. The radio timer is typically used as the timing base in wireless network communication using the 32-bit timing word as the network time. The radio timer is synchronized with the RTC by using a dedicated radio API when the device radio is turned on or off. This ensures that for a network stack, the radio timer seems to always be running when the radio is enabled. The radio timer is in most cases used indirectly through the trigger time fields in the radio APIs and should only be used when running the accurate 48 MHz high frequency crystal is the source of SCLK_HF.

Watchdog timer

The watchdog timer is used to regain control if the system operates incorrectly due to software errors. It is typically used to generate an interrupt to and reset of the device for the case where periodic monitoring of the system components and tasks fails to verify proper functionality. The watchdog timer runs on a 1.5 MHz clock rate and cannot be stopped once enabled. The watchdog timer pauses to run in Standby power mode and when a debugger halts the device.

6.8 Serial Peripherals and I/O

The SSIs are synchronous serial interfaces that are compatible with SPI, MICROWIRE, and TI's synchronous serial interfaces. The SSIs support both SPI master and slave up to 4 MHz. The SSI modules support configurable phase and polarity.

The UARTs implement universal asynchronous receiver and transmitter functions. They support flexible baud-rate generation up to a maximum of 3 Mbps.

The I²S interface is used to handle digital audio and can also be used to interface pulse-density modulation microphones (PDM).

The I²C interface is also used to communicate with devices compatible with the I²C standard. The I²C interface can handle 100 kHz and 400 kHz operation, and can serve as both master and slave.

The I/O controller (IOC) controls the digital I/O pins and contains multiplexer circuitry to allow a set of peripherals to be assigned to I/O pins in a flexible manner. All digital I/Os are interrupt and wake-up capable, have a programmable pullup and pulldown function, and can generate an interrupt on a negative or positive edge (configurable). When configured as an output, pins can function as either push-pull or open-drain. Five GPIOs have high-drive capabilities, which are marked in **bold** in Section 4. All digital peripherals can be connected to any digital pin on the device.

For more information, see the CC13x2, CC26x2 SimpleLink™ Wireless MCU Technical Reference Manual.

6.9 Battery and Temperature Monitor

A combined temperature and battery voltage monitor is available in the CC2652P device. The battery and temperature monitor allows an application to continuously monitor on-chip temperature and supply voltage and respond to changes in environmental conditions as needed. The module contains window comparators to interrupt the system CPU when temperature or supply voltage go outside defined windows. These events can also be used to wake up the device from Standby mode through the Always-On (AON) event fabric.

6.10 µDMA

The device includes a direct memory access (μ DMA) controller. The μ DMA controller provides a way to offload data-transfer tasks from the system CPU, thus allowing for more efficient use of the processor and the available bus bandwidth. The μ DMA controller can perform a transfer between memory and peripherals. The μ DMA controller has dedicated channels for each supported on-chip module and can be programmed to automatically perform transfers between peripherals and memory when the peripheral is ready to transfer more data.

Some features of the µDMA controller include the following (this is not an exhaustive list):

- Highly flexible and configurable channel operation of up to 32 channels
- Transfer modes: memory-to-memory, memory-to-peripheral, peripheral-to-memory, and peripheral-to-peripheral
- Data sizes of 8, 16, and 32 bits
- Ping-pong mode for continuous streaming of data

6.11 Debug

The on-chip debug support is done through a dedicated cJTAG (IEEE 1149.7) or JTAG (IEEE 1149.1) interface. The device boots by default into cJTAG mode and must be reconfigured to use 4-pin JTAG.

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6.12 Power Management

To minimize power consumption, the CC2652P supports a number of power modes and power management features (see Table 6-1).

Table 6-1. Power Modes

MODE	SOFT	RESET PIN			
MODE	ACTIVE	IDLE	STANDBY	SHUTDOWN	HELD
CPU	Active	Off	Off	Off	Off
Flash	On	Available	Off	Off	Off
SRAM	On	On	Retention	Off	Off
Supply System	On	On	Duty Cycled	Off	Off
Register and CPU retention	Full	Full	Partial	No	No
SRAM retention	Full	Full	Full	No	No
48 MHz high-speed clock (SCLK_HF)	XOSC_HF or RCOSC_HF	XOSC_HF or RCOSC_HF	Off	Off	Off
2 MHz medium-speed clock (SCLK_MF)	RCOSC_MF	RCOSC_MF	Available	Off	Off
32 kHz low-speed clock (SCLK_LF)	XOSC_LF or RCOSC_LF	XOSC_LF or RCOSC_LF	XOSC_LF or RCOSC_LF	Off	Off
Peripherals	Available	Available	Off	Off	Off
Sensor Controller	Available	Available	Available	Off	Off
Wake-up on RTC	Available	Available	Available	Off	Off
Wake-up on pin edge	Available	Available	Available	Available	Off
Wake-up on reset pin	On	On	On	On	On
Brownout detector (BOD)	On	On	Duty Cycled	Off	Off
Power-on reset (POR)	On	On	On	Off	Off
Watchdog timer (WDT)	Available	Available	Paused	Off	Off

In **Active** mode, the application system CPU is actively executing code. Active mode provides normal operation of the processor and all of the peripherals that are currently enabled. The system clock can be any available clock source (see Table 6-1).

In **Idle** mode, all active peripherals can be clocked, but the Application CPU core and memory are not clocked and no code is executed. Any interrupt event brings the processor back into active mode.

In **Standby** mode, only the always-on (AON) domain is active. An external wake-up event, RTC event, or Sensor Controller event is required to bring the device back to active mode. MCU peripherals with retention do not need to be reconfigured when waking up again, and the CPU continues execution from where it went into standby mode. All GPIOs are latched in standby mode.

In **Shutdown** mode, the device is entirely turned off (including the AON domain and Sensor Controller), and the I/Os are latched with the value they had before entering shutdown mode. A change of state on any I/O pin defined as a *wake from shutdown pin* wakes up the device and functions as a reset trigger. The CPU can differentiate between reset in this way and reset-by-reset pin or power-on reset by reading the reset status register. The only state retained in this mode is the latched I/O state and the flash memory contents.

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The Sensor Controller is an autonomous processor that can control the peripherals in the Sensor Controller independently of the system CPU. This means that the system CPU does not have to wake up, for example to perform an ADC sampling or poll a digital sensor over SPI, thus saving both current and wake-up time that would otherwise be wasted. The Sensor Controller Studio tool enables the user to program the Sensor Controller, control its peripherals, and wake up the system CPU as needed. All Sensor Controller peripherals can also be controlled by the system CPU.

NOTE

The power, RF and clock management for the CC2652P device require specific configuration and handling by software for optimized performance. This configuration and handling is implemented in the TI-provided drivers that are part of the CC2652P software development kit (SDK). Therefore, TI highly recommends using this software framework for all application development on the device. The complete SDK with TI-RTOS (optional), device drivers, and examples are offered free of charge in source code.

6.13 Clock Systems

The CC2652P device has several internal system clocks.

The 48 MHz SCLK HF is used as the main system (MCU and peripherals) clock. This can be driven by the internal 48 MHz RC Oscillator (RCOSC HF) or an external 48 MHz crystal (XOSC HF). Radio operation requires an external 48 MHz crystal.

SCLK MF is an internal 2 MHz clock that is used by the Sensor Controller in low-power mode and also for internal power management circuitry. The SCLK_MF clock is always driven by the internal 2 MHz RC Oscillator (RCOSC MF).

SCLK LF is the 32.768 kHz internal low-frequency system clock. It can be used by the Sensor Controller for ultra-low-power operation and is also used for the RTC and to synchronize the radio timer before or after Standby power mode. SCLK LF can be driven by the internal 32.8 kHz RC Oscillator (RCOSC LF), a 32.768 kHz watch-type crystal, or a clock input on any digital IO.

When using a crystal or the internal RC oscillator, the device can output the 32 kHz SCLK LF signal to other devices, thereby reducing the overall system cost.

6.14 Network Processor

Depending on the product configuration, the CC2652P device can function as a wireless network processor (WNP - a device running the wireless protocol stack with the application running on a separate host MCU), or as a system-on-chip (SoC) with the application and protocol stack running on the system CPU inside the device.

In the first case, the external host MCU communicates with the device using SPI or UART. In the second case, the application must be written according to the application framework supplied with the wireless protocol stack.

7 Application, Implementation, and Layout

NOTE

Information in the following Applications section is not part of the TI component specification, and TI does not warrant its accuracy or completeness. TI's customers are responsible for determining suitability of components for their purposes. Customers should validate and test their design implementation to confirm system functionality.

For general design guidelines and hardware configuration guidelines, refer to CC13xx/CC26xx Hardware Configuration and PCB Design Considerations Application Report.

For optimum RF performance, especially when using the high-power PA, it is important to accurately follow the reference design with respect to component values and layout. Failure to do so may lead to reduced RF performance due to balun mismatch. The amplitude- and phase balance through the balun must be <1 dB and <6 degrees, respectively.

PCB stack-up is also critical for proper operation. The CC1352P EVMs and characterization boards are using a finished thickness between the top layer (RF signals) and layer 2 (ground plane) of 175 μ m. It is very important to use the same substrate thickness, or slightly thicker, in an end product implementing the CC2652P device.

7.1 Reference Designs

The following reference designs should be followed closely when implementing designs using the CC2652P device.

Special attention must be paid to RF component placement, decoupling capacitors and DCDC regulator components, as well as ground connections for all of these.

All the CC1352P device reference designs are also applicable to the CC2652P device by simply disregarding the sub-1 GHz RF circuitry. For the CC2652P device, pins 3 and 4 must be left unconnected.

The high-power PA requires a specific RF matching to be able to run at 10 dBm output power. Refer to the application note Optimizing the SimpleLink CC1352P for Coin Cell Operation at 10 dBm Output Power for details.

CC1352PEM-XD7793-XD24-PA24 Design Files

The CC1352PEM-XD7793-XD24-PA24 reference design provides schematic, layout and production files for the characterization board used for deriving the performance number found in this document. This board includes tuning for 2.4 GHz on the high-power PA output. For the CC2652P device, the sub-1 GHz RF circuitry can be disregarded.

LAUNCHXL-CC1352P-2 Design Files

Detailed schematics and layouts for the multi-band CC1352P LaunchPad evaluation board featuring 2.4 GHz RF matching on the 20 dBm PA output and up to 14 dBm TX power at 868/915 MHz.

For CC2652P, the sub-1 GHz RF circuitry can be disregarded.

Sub-1 GHz and 2.4 GHz Antenna Kit for LaunchPad™ Development Kit and SensorTag

The antenna kit allows real-life testing to identify the optimal antenna for your application. The antenna kit includes 16 antennas for frequencies from 169 MHz to 2.4 GHz, including:

- PCB antennas
- Helical antennas
- Chip antennas
- Dual-band antennas for 868 MHz and 915 MHz combined with 2.4 GHz

The antenna kit includes a JSC cable to connect to the Wireless MCU LaunchPad Development Kits and SensorTags.



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Device and Documentation Support

TI offers an extensive line of development tools. Tools and software to evaluate the performance of the device, generate code, and develop solutions are listed as follows.

8.1 **Tools and Software**

The CC2652P device is supported by a variety of software and hardware development tools.

Development Kit

CC1352P-2 LaunchPad™ Development Kit

The CC1352P-2 LaunchPad™ Development Kit enables development of high-performance wireless applications in the 863 - 930 MHz and 2.4 GHz frequency bands that benefit from low-power operation. The kit features the CC1352P multi-band and multiprotocol SimpleLink Wireless MCU with an integrated High-Power Amplifier. The kit works with the LaunchPad ecosystem, easily enabling additional functionality like sensors, display, and more. The builtin EnergyTrace[™] software is an energy-based code analysis tool that measures and displays the application's energy profile and helps to optimize it for ultra-low power consumption.

The RF configuration of the LaunchPad enables up to +14 dBm output power for 863 to 930 MHz and +20 dBm output power for 2.4 GHz.

Software

SimpleLink™ CC13X2-CC26X2 SDK

The SimpleLink CC13X2-CC26X2 Software Development Kit (SDK) provides a complete package for the development of wireless applications on the CC13X2 / CC26X2 family of devices. The SDK includes a comprehensive software package for the CC2652P device, including the following protocol stacks:

- Bluetooth Low Energy 4 and 5
- Thread (based on OpenThread)
- Zigbee 3.0
- TI 15.4-Stack an IEEE 802.15.4-based star networking solution for Sub-1 GHz and 2.4 GHz
- EasyLink a large set of building blocks for building proprietary RF software stacks
- Multiprotocol support concurrent operation between stacks using the Dynamic Multiprotocol Manager (DMM)

The SimpleLink CC13X2-CC26X2 SDK is part of Tl's SimpleLink MCU platform, offering a single development environment that delivers flexible hardware, software and tool options for customers developing wired and wireless applications. For more information about the SimpleLink MCU Platform, visit http://www.ti.com/simplelink.

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TEXAS INSTRUMENTS

Development Tools

Code Composer Studio™ Integrated Development Environment (IDE)

Code Composer Studio is an integrated development environment (IDE) that supports TI's Microcontroller and Embedded Processors portfolio. Code Composer Studio comprises a suite of tools used to develop and debug embedded applications. It includes an optimizing C/C++ compiler, source code editor, project build environment, debugger, profiler, and many other features. The intuitive IDE provides a single user interface taking you through each step of the application development flow. Familiar tools and interfaces allow users to get started faster than ever before. Code Composer Studio combines the advantages of the Eclipse® software framework with advanced embedded debug capabilities from TI resulting in a compelling feature-rich development environment for embedded developers.

CCS has support for all SimpleLink Wireless MCUs and includes support for EnergyTrace™ software (application energy usage profiling). A real-time object viewer plugin is available for TI-RTOS, part of the SimpleLink SDK.

Code Composer Studio is provided free of charge when used in conjunction with the XDS debuggers included on a LaunchPad Development Kit.

Code Composer Studio™ Cloud IDE

Code Composer Studio (CCS) Cloud is a web-based IDE that allows you to create, edit and build CCS and EnergiaTM projects. After you have successfully built your project, you can download and run on your connected LaunchPad. Basic debugging, including features like setting breakpoints and viewing variable values is now supported with CCS Cloud.

IAR Embedded Workbench® for Arm®

IAR Embedded Workbench[®] is a set of development tools for building and debugging embedded system applications using assembler, C and C++. It provides a completely integrated development environment that includes a project manager, editor, and build tools. IAR has support for all SimpleLink Wireless MCUs. It offers broad debugger support, including XDS110, IAR I-jetTM and Segger J-LinkTM. A real-time object viewer plugin is available for TI-RTOS, part of the SimpleLink SDK. IAR is also supported out-of-the-box on most software examples provided as part of the SimpleLink SDK.

A 30-day evaluation or a 32 KB size-limited version is available through iar.com.

SmartRF™ Studio

SmartRF™ Studio is a Windows® application that can be used to evaluate and configure SimpleLink Wireless MCUs from Texas Instruments. The application will help designers of RF systems to easily evaluate the radio at an early stage in the design process. It is especially useful for generation of configuration register values and for practical testing and debugging of the RF system. SmartRF Studio can be used either as a standalone application or together with applicable evaluation boards or debug probes for the RF device. Features of the SmartRF Studio include:

- Link tests send and receive packets between nodes
- Antenna and radiation tests set the radio in continuous wave TX and RX states
- Export radio configuration code for use with the TI SimpleLink SDK RF driver
- Custom GPIO configuration for signaling and control of external switches

Sensor Controller Studio

Sensor Controller Studio is used to write, test and debug code for the Sensor Controller peripheral. The tool generates a Sensor Controller Interface driver, which is a set of C source files that are compiled into the System CPU application. These source files also contain the Sensor Controller binary image and allow the System CPU application to control and exchange data with the Sensor Controller. Features of the Sensor Controller Studio include:

- Ready-to-use examples for several common use cases
- Full toolchain with built-in compiler and assembler for programming in a C-like programming language
- Provides rapid development by using the integrated sensor controller task testing and debugging functionality, including visualization of sensor data and verification of algorithms

CCS UniFlash

CCS UniFlash is a standalone tool used to program on-chip flash memory on TI MCUs. UniFlash has a GUI, command line, and scripting interface. CCS UniFlash is available free of charge.

8.1.1 SimpleLink™ Microcontroller Platform

The SimpleLink microcontroller platform sets a new standard for developers with the broadest portfolio of wired and wireless Arm® MCUs (System-on-Chip) in a single software development environment. Delivering flexible hardware, software and tool options for your IoT applications. Invest once in the SimpleLink software development kit and use throughout your entire portfolio. Learn more on ti.com/simplelink.

8.2 Documentation Support

To receive notification of documentation updates on data sheets, errata, application notes and similar, navigate to the device product folder on ti.com/product/CC2652P. In the upper right corner, click on *Alert me* to register and receive a weekly digest of any product information that has changed. For change details, review the revision history included in any revised document.

The current documentation that describes the MCU, related peripherals, and other technical collateral is listed as follows.

TI Resource Explorer

TI Resource Explorer

Software examples, libraries, executables, and documentation are available for your device and development board.

Errata

CC2652P Silicon Errata

The silicon errata describes the known exceptions to the functional specifications for each silicon revision of the device and description on how to recognize a device revision.

Application Reports

All application reports for the CC2652P device are found on the device product folder at: ti.com/product/CC2652P/technicaldocuments.

Technical Reference Manual (TRM)

CC13x2, CC26x2 SimpleLink™ Wireless MCU TRM

The TRM provides a detailed description of all modules and peripherals available in the device family.

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8.3 Support Resources

TI E2E™ support forums are an engineer's go-to source for fast, verified answers and design help — straight from the experts. Search existing answers or ask your own question to get the quick design help you need.

Linked content is provided "AS IS" by the respective contributors. They do not constitute TI specifications and do not necessarily reflect TI's views; see TI's Terms of Use.

8.4 Trademarks

SimpleLink, SmartRF, LaunchPad, EnergyTrace, Code Composer Studio, E2E are trademarks of Texas Instruments.

Arm, Cortex, Arm Thumb are registered trademarks of Arm Limited (or its subsidiaries).

Bluetooth is a registered trademark of Bluetooth SIG Inc.

Eclipse is a registered trademark of Eclipse Foundation.

CoreMark is a registered trademark of Embedded Microprocessor Benchmark Consortium.

I-jet is a trademark of IAR Systems AB.

IAR Embedded Workbench is a registered trademark of IAR Systems AB.

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Wi-SUN is a registered trademark of Wi-SUN Alliance Inc.

Zigbee is a registered trademark of Zigbee Alliance Inc.

All other trademarks are the property of their respective owners.

8.5 Electrostatic Discharge Caution



This integrated circuit can be damaged by ESD. Texas Instruments recommends that all integrated circuits be handled with appropriate precautions. Failure to observe proper handling and installation procedures can cause damage.

ESD damage can range from subtle performance degradation to complete device failure. Precision integrated circuits may be more susceptible to damage because very small parametric changes could cause the device not to meet its published specifications.

8.6 Glossary

TI Glossary This glossary lists and explains terms, acronyms, and definitions.

9 Mechanical, Packaging, and Orderable Information

9.1 Packaging Information

The following pages include mechanical packaging and orderable information. This information is the most current data available for the designated devices. This data is subject to change without notice and revision of this document. For browser-based versions of this data sheet, refer to the left-hand navigation.



PACKAGE OPTION ADDENDUM

2-Nov-2019

PACKAGING INFORMATION

Orderable Device	Status	Package Type	_	Pins	_	Eco Plan	Lead/Ball Finish	MSL Peak Temp	Op Temp (°C)	Device Marking	Samples
	(1)		Drawing		Qty	(2)	(6)	(3)		(4/5)	
CC2652P1FRGZR	ACTIVE	VQFN	RGZ	48	2500	Green (RoHS & no Sb/Br)	CU NIPDAU CU NIPDAUAG	Level-3-260C-168 HR	-40 to 85	CC2652 P1F	Samples

(1) The marketing status values are defined as follows:

ACTIVE: Product device recommended for new designs.

LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.

NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.

PREVIEW: Device has been announced but is not in production. Samples may or may not be available.

OBSOLETE: TI has discontinued the production of the device.

(2) RoHS: TI defines "RoHS" to mean semiconductor products that are compliant with the current EU RoHS requirements for all 10 RoHS substances, including the requirement that RoHS substance do not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, "RoHS" products are suitable for use in specified lead-free processes. TI may reference these types of products as "Pb-Free".

RoHS Exempt: TI defines "RoHS Exempt" to mean products that contain lead but are compliant with EU RoHS pursuant to a specific EU RoHS exemption.

Green: TI defines "Green" to mean the content of Chlorine (CI) and Bromine (Br) based flame retardants meet JS709B low halogen requirements of <=1000ppm threshold. Antimony trioxide based flame retardants must also meet the <=1000ppm threshold requirement.

- (3) MSL, Peak Temp. The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.
- (4) There may be additional marking, which relates to the logo, the lot trace code information, or the environmental category on the device.
- (5) Multiple Device Markings will be inside parentheses. Only one Device Marking contained in parentheses and separated by a "~" will appear on a device. If a line is indented then it is a continuation of the previous line and the two combined represent the entire Device Marking for that device.
- (6) Lead/Ball Finish Orderable Devices may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead/Ball Finish values may wrap to two lines if the finish value exceeds the maximum column width.

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In no event shall TI's liability arising out of such information exceed the total purchase price of the TI part(s) at issue in this document sold by TI to Customer on an annual basis.

PACKAGE MATERIALS INFORMATION

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TAPE AND REEL INFORMATION





	Dimension designed to accommodate the component width
	Dimension designed to accommodate the component length
K0	Dimension designed to accommodate the component thickness
W	Overall width of the carrier tape
P1	Pitch between successive cavity centers

QUADRANT ASSIGNMENTS FOR PIN 1 ORIENTATION IN TAPE



*All dimensions are nominal

Device	Package Type	Package Drawing			Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
CC2652P1FRGZR	VQFN	RGZ	48	2500	330.0	16.4	7.3	7.3	1.1	12.0	16.0	Q2

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*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
CC2652P1FRGZR	VQFN	RGZ	48	2500	336.6	336.6	31.8

7 x 7, 0.5 mm pitch

PLASTIC QUADFLAT PACK- NO LEAD

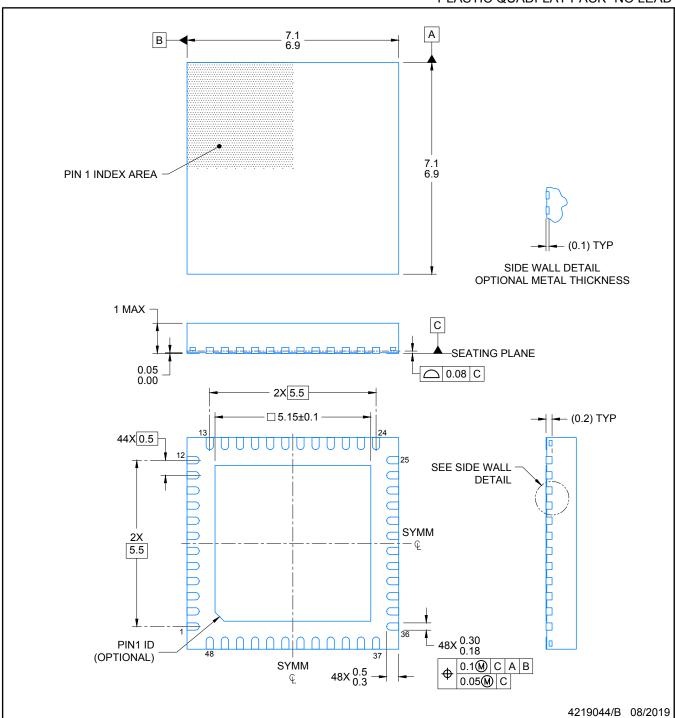


Images above are just a representation of the package family, actual package may vary. Refer to the product data sheet for package details.

4224671/A



PLASTIC QUADFLAT PACK- NO LEAD

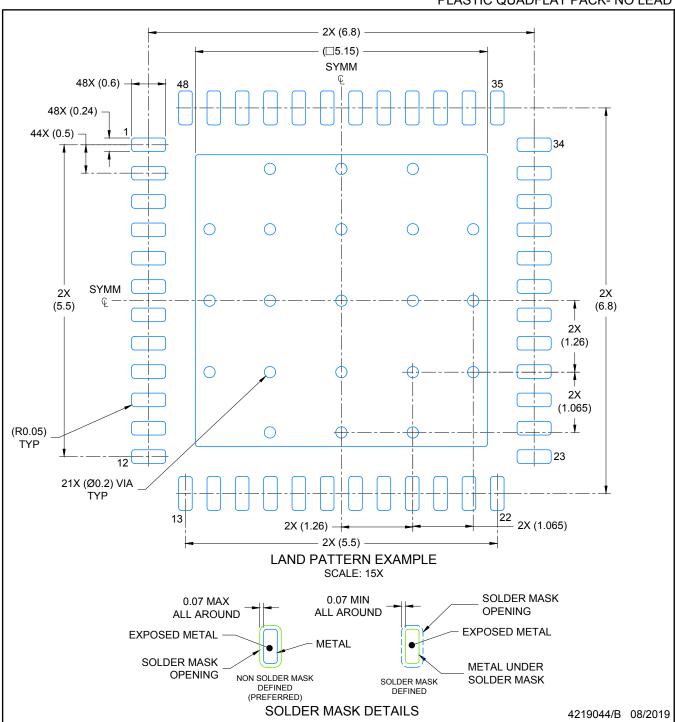


NOTES:

- 1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.
- 2. This drawing is subject to change without notice.
- 3. The package thermal pad must be soldered to the printed circuit board for optimal thermal and mechanical performance.



PLASTIC QUADFLAT PACK- NO LEAD

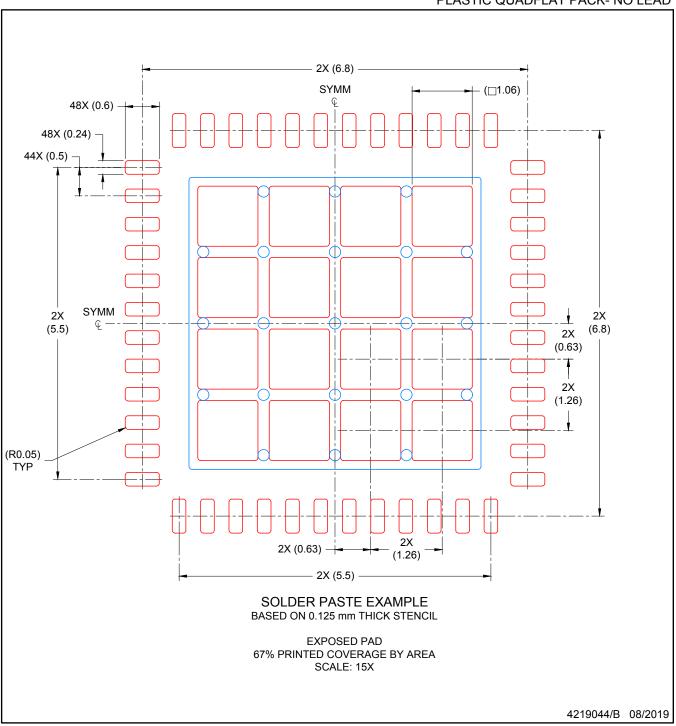


NOTES: (continued)

- 4. This package is designed to be soldered to a thermal pad on the board. For more information, see Texas Instruments literature number SLUA271 (www.ti.com/lit/slua271).
- 5. Vias are optional depending on application, refer to device data sheet. If any vias are implemented, refer to their locations shown on this view. It is recommended that vias under paste be filled, plugged or tented.



PLASTIC QUADFLAT PACK- NO LEAD



NOTES: (continued)

6. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.



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